MAX 10 FPGA Device Datasheet

2015.05.04

M10-DATASHEET





This datasheet describes the electrical characteristics, switching characteristics, configuration specifications, and timing for MAX® 10 devices.

Table 1: MAX 10 Device Grades and Speed Grades Supported

Device Grade	Speed Grade Supported
Commercial	-C7-C8 (slowest)
Industrial	-I6 (fastest)-I7
Automotive	-A7

Note: The –I6 speed grade MAX 10 FPGA device option is not available by default in the Quartus[®] II software. Contact your local Altera sales representatives for support.

Related Information

Device Ordering Information, MAX 10 FPGA Device Overview

Provides more information about the densities and packages of devices in the MAX 10.

Electrical Characteristics

The following sections describe the operating conditions and power consumption of MAX 10 devices.

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Operating Conditions

MAX 10 devices are rated according to a set of defined parameters. To maintain the highest possible performance and reliability of the MAX 10 devices, you must consider the operating requirements described in this section.

Absolute Maximum Ratings

This section defines the maximum operating conditions for MAX 10 devices. The values are based on experiments conducted with the devices and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied for these conditions.

Caution: Conditions outside the range listed in the absolute maximum ratings tables may cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse effects on the device.

Single Supply Devices Absolute Maximum Ratings

Table 2: Absolute Maximum Ratings for MAX 10 Single Supply Devices—Preliminary

Symbol	Parameter	Min	Max	Unit
V _{CC_ONE}	Supply voltage for core and periphery through on- die voltage regulator	-0.5	3.9	V
V _{CCIO}	Supply voltage for input and output buffers	-0.5	3.9	V
V _{CCA}	Supply voltage for phase-locked loop (PLL) regulator and analog-to-digital converter (ADC) block (analog)	-0.5	3.9	V

Dual Supply Devices Absolute Maximum Ratings

Table 3: Absolute Maximum Ratings for MAX 10 Dual Supply Devices—Preliminary

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply voltage for core and periphery	-0.5	1.63	V
V_{CCIO}	Supply voltage for input and output buffers	-0.5	3.9	V
$ m V_{CCA}$	Supply voltage for PLL regulator (analog)	-0.5	3.41	V
V_{CCD_PLL}	Supply voltage for PLL regulator (digital)	-0.5	1.63	V



Symbol	Parameter	Min	Max	Unit
$ m V_{CCA_ADC}$	Supply voltage for ADC analog block	-0.5	3.41	V
V _{CCINT}	Supply voltage for ADC digital block	-0.5	1.63	V

Absolute Maximum Ratings

Table 4: Absolute Maximum Ratings for MAX 10 Devices—Preliminary

Symbol	Parameter	Min	Max	Unit
V_{I}	DC input voltage	-0.5	4.12	V
I_{OUT}	DC output current per pin	-25	25	mA
T_{STG}	Storage temperature	-65	150	°C
T_{J}	Operating junction temperature	-40	125	°C

Maximum Allowed Overshoot During Transitions over a 11.4-Year Time Frame

Table 5: Maximum Allowed Overshoot During Transitions over a 11.4-Year Time Frame for MAX 10 Devices

Condition (V)	Overshoot Duration as % of High Time	Unit
4.12	100.0	%
4.17	11.7	%
4.22	7.1	%
4.27	4.3	%
4.32	2.6	%
4.37	1.6	%
4.42	1.0	%
4.47	0.6	%
4.52	0.3	%



Condition (V)	Overshoot Duration as % of High Time	Unit
4.57	0.2	%

Recommended Operating Conditions

This section lists the functional operation limits for the AC and DC parameters for MAX 10 devices. The tables list the steady-state voltage values expected from MAX 10 devices. Power supply ramps must all be strictly monotonic, without plateaus.

Single Supply Devices Power Supplies Recommended Operating Conditions

Table 6: Power Supplies Recommended Operating Conditions for MAX 10 Single Supply Devices—Preliminary

Symbol	Parameter	Condition	Min	Тур	Max	Unit
$V_{CC_ONE}^{(1)}$	Supply voltage for core and periphery through on-die voltage regulator	_	2.85/3.135	3.0/3.3	3.15/3.465	V
		3.3 V	3.135	3.3	3.465	V
		3.0 V	2.85	3	3.15	V
		2.5 V	2.375	2.5	2.625	V
$V_{\rm CCIO}^{(2)}$	Supply voltage for input and output buffers	1.8 V	1.71	1.8	1.89	V
		1.5 V	1.425	1.5	1.575	V
		1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V _{CCA} (1)	Supply voltage for PLL regulator and ADC block (analog)	_	2.85/3.135	3.0/3.3	3.15/3.465	V



 $^{^{(1)}~}V_{CCA}$ must be connected to V_{CC_ONE} through a filter.

 $^{^{(2)}}$ V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities.

Dual Supply Devices Power Supplies Recommended Operating Conditions

Table 7: Power Supplies Recommended Operating Conditions for MAX 10 Dual Supply Devices—Preliminary

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V_{CC}	Supply voltage for core and periphery	_	1.15	1.2	1.25	V
		3.3 V	3.135	3.3	3.465	V
		3.0 V	2.85	3	3.15	V
		2.5 V	2.375	2.5	2.625	V
$V_{\rm CCIO}^{~(3)}$	Supply voltage for input and output buffers	1.8 V	1.71	1.8	1.89	V
		1.5 V	1.425	1.5	1.575	V
		1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V _{CCA} ⁽⁴⁾	Supply voltage for PLL regulator (analog)	_	2.375	2.5	2.625	V
V _{CCD_PLL} ⁽⁵⁾	Supply voltage for PLL regulator (digital)	_	1.15	1.2	1.25	V
V _{CCA_ADC}	Supply voltage for ADC analog block	_	2.375	2.5	2.625	V
V_{CCINT}	Supply voltage for ADC digital block	_	1.15	1.2	1.25	V

Recommended Operating Conditions

Table 8: Recommended Operating Conditions for MAX 10 Devices—Preliminary

Symbol	Parameter	Condition	Min	Max	Unit
V_{I}	DC input voltage	_	-0.5	3.6	V

 $^{^{(3)}}$ V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities.



⁽⁴⁾ All V_{CCA} pins must be powered to 2.5 V (even when PLLs are not used), and must be powered up and powered down at the same time.

⁽⁵⁾ V_{CCD PLL} must always be connected to V_{CC} through a decoupling capacitor and ferrite bead.

Symbol	Parameter	Condition	Min	Max	Unit
V _O	Output voltage for I/O pins	_	0	V _{CCIO}	V
		Commercial	0	85	°C
T_J	Operating junction temperature	Industrial	-40	100	°C
		Automotive	-40	125	°C
		Standard POR ⁽⁶⁾	200 μs	50 ms	_
t_{RAMP}	Power supply ramp time	Fast POR (7)	200 μs	3 ms	_
		Instant-on	200 μs	3 ms	_
I_{Diode}	Magnitude of DC current across PCI clamp diode when enabled	_	_	10	mA

Programming/Erasure Specifications

Table 9: Programming/Erasure Specifications for MAX 10 Devices—Preliminary

This table shows the programming cycles and data retention duration of the user flash memory (UFM) and configuration flash memory (CFM) blocks.

Erase and reprogram cycles (E/P) ⁽⁸⁾ (Cycles/page)	Temperature (°C)	Data retention duration (Years)
10,000	85	20
10,000	100	10

DC Characteristics

I/O Pin Leakage Current

The values in the table are specified for normal device operation. The values vary during device power-up. This applies for all V_{CCIO} settings (3.3, 3.0, 2.5, 1.8, 1.5, 1.35, and 1.2 V).



⁽⁶⁾ Each individual power supply should reach the recommended operating range within 50 ms.

⁽⁷⁾ Each individual power supply should reach the recommended operating range within 3 ms.

⁽⁸⁾ The number of E/P cycles applies to the smallest possible flash block that can be erased or programmed in each MAX 10 device. Each MAX 10 device has multiple flash pages per device.

10 μA I/O leakage current limit is applicable when the internal clamping diode is off. A higher current can be the observed when the diode is on.

Input channel leakage of ADC I/O pins due to hot socket is up to maximum of 1.8 mA. The input channel leakage occurs when the ADC IP core is enabled or disabled. This is applicable to all MAX 10 devices with ADC IP core, which are 10M04, 10M08, 10M16, 10M25, 10M40, and 10M50 devices. The ADC I/O pins are in Bank 1A.

Table 10: I/O Pin Leakage Current for MAX 10 Devices—Preliminary

Symbol	Parameter	Condition	Min	Max	Unit
I_{I}	Input pin leakage current	$V_{I} = 0 V \text{ to } V_{CCIOMAX}$	-10	10	μΑ
I _{OZ}	Tristated I/O pin leakage current	$V_O = 0 V \text{ to } V_{CCIOMAX}$	-10	10	μΑ

Bus Hold Parameters

Bus hold retains the last valid logic state after the source driving it either enters the high impedance state or is removed. Each I/O pin has an option to enable bus hold in user mode. Bus hold is always disabled in configuration mode.

Table 11: Bus Hold Parameters for MAX 10 Devices—Preliminary

		V _{CCIO} (V)												
Parameter	Condition	1.2		1	1.5		1.8		2.5		3	3.3		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus-hold low, sustaining current	$V_{IN} > V_{IL}$ (maximum)	8	_	12	_	30	_	50	_	70	_	70	_	μΑ
Bus-hold high, sustaining current	$V_{IN} < V_{IL}$ (minimum)	-8	_	-12	_	-30	_	-50	_	-70	_	-70	_	μΑ
Bus-hold low, overdrive current	$\begin{array}{c} 0 \; \mathrm{V} < \mathrm{V_{IN}} < \\ \mathrm{V_{CCIO}} \end{array}$	_	125	_	175	_	200	_	300	_	500	_	500	μΑ
Bus-hold high, overdrive current	$\begin{array}{c} 0 \; \mathrm{V} < \mathrm{V_{IN}} < \\ \mathrm{V_{CCIO}} \end{array}$	_	-125	_	-175	_	-200	_	-300	_	-500	_	-500	μΑ
Bus-hold trip point	_	0.3	0.9	0.375	1.125	0.68	1.07	0.7	1.7	0.8	2	0.8	2	V



Series OCT without Calibration Specifications

Table 12: Series OCT without Calibration Specifications for MAX 10 Devices—Preliminary

This table shows the variation of on-chip termination (OCT) without calibration across process, voltage, and temperature (PVT).

Description	V _{CCIO} (V)	Resistance	Unit	
Description	ACCIO (A)	-C7, -I6, -I7, -A7	-C8	Offic
	3.00	±35	±30	%
	2.50	±35	±30	%
Series OCT without calibration	1.80	±40	±35	%
Series Oct without campiation	1.50	±40	±40	%
	1.35	±40	±50	%
	1.20	±45	±60	%

Series OCT with Calibration at Device Power-Up Specifications

Table 13: Series OCT with Calibration at Device Power-Up Specifications for MAX 10 Devices—Preliminary

OCT calibration is automatically performed at device power-up for OCT enabled I/Os.

Description	V _{CCIO} (V)	Calibration Accuracy	Unit
	3.00	±12	%
	2.50	±12	%
Series OCT with calibration at device power-up	1.80	±12	%
Series OCT with cambration at device power-up	1.50	±12	%
	1.35	±12	%
	1.20	±12	%

OCT Variation after Calibration at Device Power-Up

The OCT resistance may vary with the variation of temperature and voltage after calibration at device power-up.



Use the following table and equation to determine the final OCT resistance considering the variations after calibration at device power-up.

Table 14: OCT Variation after Calibration at Device Power-Up for MAX 10 Devices—Preliminary

This table lists the change percentage of the OCT resistance with voltage and temperature.

Desccription	Nominal Voltage	dR/dT (%/°C)	dR/dV (%/mV)		
	3.00	0.25	-0.027		
	2.50	0.245	-0.04		
OCT variation after calibraiton at device power-up	1.80	0.242	-0.079		
OCT variation after campration at device power-up	1.50	0.235	-0.125		
	1.35	0.229	-0.16		
	1.20	0.197	-0.208		

Figure 1: Equation for OCT Resistance after Calibration at Device Power-Up

$$\Delta R_V = (V_2 - V_1) \times 1000 \times dR/dV$$

$$\Delta R_T = (T_2 - T_1) \times dR/dT$$
 For $\Delta R_X < 0$; $MF_X = 1/(|\Delta R_X|/100 + 1)$ For $\Delta R_X > 0$; $MF_X = \Delta R_X/100 + 1$
$$MF = MF_V \times MF_T$$

$$R_{final} = R_{initial} \times MF$$



The definitions for equation are as follows:

- T₁ is the initial temperature.
- T₂ is the final temperature.
- MF is multiplication factor.
- R_{initial} is initial resistance.
- R_{final} is final resistance.
- Subscript x refers to both V and T.
- ΔR_V is variation of resistance with voltage.
- ΔR_T is variation of resistance with temperature.
- dR/dT is the change percentage of resistance with temperature after calibration at device power-up.
- dR/dV is the change percentage of resistance with voltage after calibration at device power-up.
- V_1 is the initial voltage.
- V₂ is final voltage.

The following figure shows the example to calculate the change of 50 Ω I/O impedance from 25°C at 3.0 V to 85°C at 3.15 V.

Figure 2: Example for OCT Resistance Calculation after Calibration at Device Power-Up

$$\Delta R_V = (3.15 - 3) \times 1000 \times -0.027 = -4.05$$

 $\Delta R_T = (85 - 25) \times 0.25 = 15$

Because ΔR_V is negative,

$$MF_V = 1/(4.05/100 + 1) = 0.961$$

Because ΔR_T is positive,

$$MF_T = 15/100 + 1 = 1.15$$

$$MF = 0.961 \times 1.15 = 1.105$$

$$R_{final} = 50 \times 1.105 = 55.25\Omega$$



Pin Capacitance

Table 15: Pin Capacitance for MAX 10 Devices—Preliminary

Symbol	Parameter	Value	Unit
C_{IOB}	Input capacitance on bottom I/O pins	8	pF
C_{IOLRT}	Input capacitance on left/right/top I/O pins	7	pF
C_{LVDSB}	Input capacitance on bottom I/O pins with dedicated LVDS output ⁽⁹⁾	8	pF
C_{ADCL}	Input capacitance on left I/O pins with ADC input (10)	9	pF
$C_{VREFLRT}$	Input capacitance on left/right/top dual purpose V_{REF} pin when used as V_{REF} or user I/O pin $^{(11)}$	48	pF
C_{VREFB}	Input capacitance on bottom dual purpose V_{REF} pin when used as V_{REF} or user I/O pin	50	pF
C_{CLKB}	Input capacitance on bottom dual purpose clock input pins (12)	7	pF
C _{CLKLRT}	Input capacitance on left/right/top dual purpose clock input pins (12)	6	pF

Internal Weak Pull-Up Resistor

All I/O pins, except configuration, test, and JTAG pins, have an option to enable weak pull-up.



⁽⁹⁾ Dedicated LVDS output buffer is only available at bottom I/O banks.

⁽¹⁰⁾ ADC pins are only available at left I/O banks.

When V_{REF} pin is used as regular input or output, F_{max} performance is reduced due to higher pin capacitance. Using the V_{REF} pin capacitance specification from device datasheet, perform SI analysis on your board setup to determine the F_{max} of your system.

^{(12) 10}M40 and 10M50 devices have dual purpose clock input pins at top/bottom I/O banks.

Table 16: Internal Weak Pull-Up Resistor for MAX 10 Devices—Preliminary

Pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO}.

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		$V_{\text{CCIO}} = 3.3 \text{ V} \pm 5\%$	7	12	18	kΩ
	Value of I/O pin pull-up resistor before	$V_{\text{CCIO}} = 3.0 \text{ V} \pm 5\%$	8	13	20	kΩ
R_ _{PU}	and during configuration, as well as user	$V_{\rm CCIO} = 2.5 \text{ V} \pm 5\%$	10	15	25	kΩ
т_р	mode if the programmable pull-up resistor option is enabled	$V_{\rm CCIO} = 1.8 \text{ V} \pm 5\%$	16	25	46	kΩ
		$V_{\rm CCIO} = 1.5 \text{ V} \pm 5\%$	20	36	82	kΩ
		$V_{\text{CCIO}} = 1.2 \text{ V} \pm 5\%$	33	82	175	kΩ

The internal weak pull-up resistor is defined in the following equation:

Figure 3: Internal Weak Pull-Up Resistor

$$R_{-PU} = (V_{CCIO} - V_I)/I_{R_{_}PU}$$

Minimum condition: -40°C; $V_{CCIO} = V_{CC} + 5\%$; $V_{I} = V_{CC} + 5\% - 50$ mV;

Typical condition: 25° C; $V_{CCIO} = V_{CC}$; $V_{I} = 0$ V;

Maximum condition: 125°C; $V_{CCIO} = V_{CC} - 5\%$; $V_{I} = 0 V$;

where $V_{\rm I}$ refers to the input voltage at the I/O pin.



Hot-Socketing Specifications

Table 17: Hot-Socketing Specifications for MAX 10 Devices—Preliminary

Symbol	Parameter	Maximum				
$I_{IOPIN(DC)}$	DC current per I/O pin	300 μΑ				
I _{IOPIN(AC)}	AC current per I/O pin	8 mA ⁽¹³⁾				

Hysteresis Specifications for Schmitt Trigger Input

MAX 10 devices support Schmitt trigger input on all I/O pins. A Schmitt trigger feature introduces hysteresis to the input signal for improved noise immunity, especially for signal with slow edge rate.

Table 18: Hysteresis Specifications for Schmitt Trigger Input for MAX 10 Devices—Preliminary

Symbol	Parameter	Condition	Minimum	Unit
V		$V_{\text{CCIO}} = 3.3 \text{ V}$	180	mV
	Hysteresis for Schmitt trigger input	V _{CCIO} = 2.5 V	150	mV
V_{HYS}		V _{CCIO} = 1.8 V	120	mV
		V _{CCIO} = 1.5 V	110	mV



The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, $|I_{IOPIN}| = C dv/dt$, in which C is I/O pin capacitance and dv/dt is the slew rate.

Figure 4: LVTTL/LVCMOS Input Standard Voltage Diagram

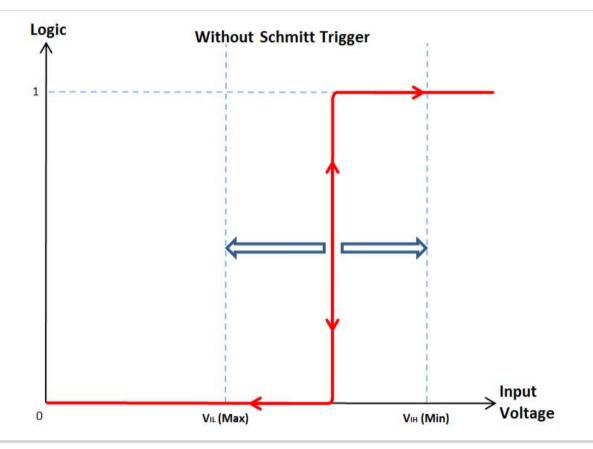
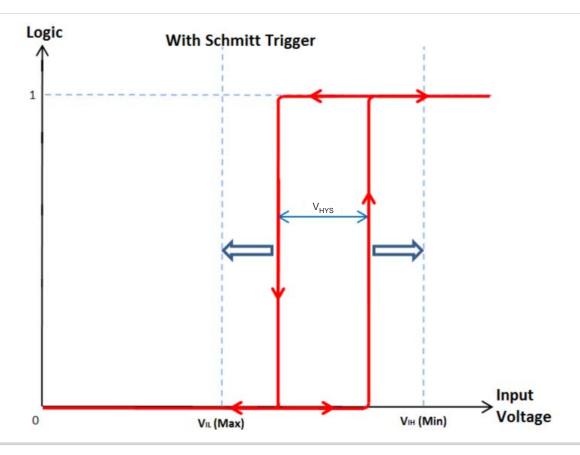




Figure 5: Schmitt Trigger Input Standard Voltage Diagram



I/O Standards Specifications

Tables in this section list input voltage (V_{IH} and V_{IL}), output voltage (V_{OH} and V_{OL}), and current drive characteristics (I_{OH} and I_{OL}) for various I/O standards supported by MAX 10 devices.

For minimum voltage values, use the minimum V_{CCIO} values. For maximum voltage values, use the maximum V_{CCIO} values.

You must perform timing closure analysis to determine the maximum achievable frequency for general purpose I/O standards.



Single-Ended I/O Standards Specifications

Table 19: Single-Ended I/O Standards Specifications for MAX 10 Devices—Preliminary

To meet the I_{OL} and I_{OH} specifications, you must set the current strength settings accordingly. For example, to meet the 3.3-V LVTTL specification (4 mA), you should set the current strength settings to 4 mA. Setting at lower current strength may not meet the I_{OL} and I_{OH} specifications in the datasheet.

I/O Standard	V _{CCIO} (V)				V _{IL} (V)		(V)	V _{OL} (V)	V _{OH} (V)	Ι (m Δ)	I _{OH} (mA)
i/O Standard	Min	Тур	Max	Min	Max	Min	Max	Max	Min	I _{OL} (mA)	I _{OH} (IIIA)
3.3 V LVTTL	3.135	3.3	3.465	-0.3	0.8	1.7	3.6	0.45	2.4	4	-4
3.3 V LVCMOS	3.135	3.3	3.465	-0.3	0.8	1.7	3.6	0.2	V _{CCIO} - 0.2	2	-2
3.0 V LVTTL	2.85	3	3.15	-0.3	0.8	1.7	V _{CCIO} + 0.3	0.45	2.4	4	-4
3.0 V LVCMOS	2.85	3	3.15	-0.3	0.8	1.7	V _{CCIO} + 0.3	0.2	V _{CCIO} – 0.2	0.1	-0.1
2.5 V LVTTL and LVCMOS	2.375	2.5	2.625	-0.3	0.7	1.7	V _{CCIO} + 0.3	0.4	2	1	-1
1.8 V LVTTL and LVCMOS	1.71	1.8	1.89	-0.3	$0.35 \times V_{\rm CCIO}$	$0.65 \times V_{\rm CCIO}$	2.25	0.45	V _{CCIO} – 0.45	2	-2
1.5 V LVCMOS	1.425	1.5	1.575	-0.3	$0.35 \times V_{\rm CCIO}$	$0.65 \times V_{\rm CCIO}$	V _{CCIO} + 0.3	$\begin{array}{c} 0.25 \times \\ V_{CCIO} \end{array}$	$0.75 \times V_{\rm CCIO}$	2	-2
1.2 V LVCMOS	1.14	1.2	1.26	-0.3	$0.35 \times V_{\rm CCIO}$	$0.65 \times V_{\rm CCIO}$	V _{CCIO} + 0.3	$\begin{array}{c} 0.25 \times \\ V_{CCIO} \end{array}$	$0.75 \times V_{\rm CCIO}$	2	-2
3.3 V Schmitt Trigger	3.135	3.3	3.465	-0.3	0.8	1.7	V _{CCIO} + 0.3	_	_	_	_
2.5 V Schmitt Trigger	2.375	2.5	2.625	-0.3	0.7	1.7	V _{CCIO} + 0.3	_	_	_	_
1.8 V Schmitt Trigger	1.71	1.8	1.89	-0.3	$\begin{array}{c} 0.35 \times \\ V_{CCIO} \end{array}$	$0.65 \times V_{\rm CCIO}$	V _{CCIO} + 0.3	_	_	_	_
1.5 V Schmitt Trigger	1.425	1.5	1.575	-0.3	$0.35 \times V_{\rm CCIO}$	$0.65 \times V_{\rm CCIO}$	V _{CCIO} + 0.3	_	_	_	_



I/O Standard		V _{CCIO} (V)		V _{IL}	(V)	V _{IH}	_I (V)	V _{OL} (V)	V _{OH} (V)	I. (mA)	I _{OH} (mA)
i/O Standard	Min	Тур	Max	Min	Max	Min	Max	Max	Min	I _{OL} (mA) I _{OH}	IOH (IIIA)
3.0 V PCI	2.85	3	3.15	_	$\begin{array}{c} 0.3 \times \\ V_{CCIO} \end{array}$	$0.5 \times V_{\rm CCIO}$	V _{CCIO} + 0.3	$\begin{array}{c} 0.1 \times \\ V_{\rm CCIO} \end{array}$	$\begin{array}{c} 0.9 \times \\ V_{\rm CCIO} \end{array}$	1.5	-0.5

Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications

Table 20: Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications for MAX 10 Devices—Preliminary

I/O Standard		V _{CCIO} (V)			V _{REF} (V)		V _{TT} (V) (14)			
i/O Standard	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
SSTL-2 Class I, II	2.375	2.5	2.625	1.19	1.25	1.31	V _{REF} - 0.04	V _{REF}	$V_{REF} + 0.04$	
SSTL-18 Class I, II	1.7	1.8	1.9	0.833	0.9	0.969	V _{REF} - 0.04	V _{REF}	$V_{REF} + 0.04$	
SSTL-15 Class I, II	1.425	1.5	1.575	$\begin{array}{c} 0.49 \times \\ V_{\rm CCIO} \end{array}$	$0.5 \times V_{CCIO}$	$0.51 \times V_{\rm CCIO}$	$0.49 \times V_{\rm CCIO}$	$0.5 \times V_{CCIO}$	$0.51 \times V_{CCIO}$	
SSTL-135 Class I, II	1.283	1.35	1.45	$\begin{array}{c} 0.49 \times \\ V_{CCIO} \end{array}$	$0.5 \times V_{CCIO}$	$0.51 \times V_{\rm CCIO}$	$\begin{array}{c} 0.49 \times \\ V_{CCIO} \end{array}$	$0.5 \times V_{CCIO}$	$0.51 \times V_{CCIO}$	
HSTL-18 Class I, II	1.71	1.8	1.89	0.85	0.9	0.95	0.85	0.9	0.95	
HSTL-15 Class I, II	1.425	1.5	1.575	0.71	0.75	0.79	0.71	0.75	0.79	
HSTL-12 Class	1.14	1.14 1.2	1.26	$V_{\rm CCIO}^{(15)}$	$0.5 \times V_{\rm CCIO}$ (15)	$0.52 \times V_{\rm CCIO}$ (15)		$0.5 \times V_{CCIO}$ —	_	
I, II	1,11	1,2	1.20	$V_{\rm CCIO}$ (16)	$0.5 \times V_{\text{CCIO}}$	$0.53 \times V_{\text{CCIO}}$		0.5 % FCCIO		

 $^{^{(14)}}$ V_{TT} of transmitting device must track V_{REF} of the receiving device.



⁽¹⁵⁾ Value shown refers to DC input reference voltage, V_{REF(DC)}.

Value shown refers to AC input reference voltage, $V_{REF(AC)}$.

I/O Standard		V _{CCIO} (V)			V _{REF} (V)		V _{TT} (V) ⁽¹⁴⁾			
1/O Standard	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
HSUL-12	1.14	1.2	1.3	$\begin{array}{c} 0.49 \times \\ V_{\rm CCIO} \end{array}$	$0.5 \times V_{CCIO}$	$\begin{array}{c} 0.51 \times \\ V_{\rm CCIO} \end{array}$	_	_	_	

Single-Ended SSTL, HSTL, and HSUL I/O Standards Signal Specifications

Table 21: Single-Ended SSTL, HSTL, and HSUL I/O Standards Signal Specifications for MAX 10 Devices—Preliminary

To meet the I_{OL} and I_{OH} specifications, you must set the current strength settings accordingly. For example, to meet the SSTL-15 Class I specification (8 mA), you should set the current strength settings to 8 mA. Setting at lower current strength may not meet the I_{OL} and I_{OH} specifications in the datasheet.

I/O Standard		_{C)} (V)		_{C)} (V)		_{C)} (V)	V _{IH(A}	•	V _{OL} (V)	V _{OH} (V)	l _{OL} (mA)	I _{OH} (mA)
i/O Staildard	Min	Max	Min	Max	Min	Max	Min	Max	Max	Min	IOL (IIIA)	IOH (IIIA)
SSTL-2 Class I	_	V _{REF} – 0.18	V _{REF} + 0.18	_	_	V _{REF} – 0.31	V _{REF} + 0.31	_	V _{TT} – 0.57	V _{TT} + 0.57	8.1	-8.1
SSTL-2 Class II	_	V _{REF} – 0.18	V _{REF} + 0.18	_	_	V _{REF} – 0.31	V _{REF} + 0.31		V _{TT} – 0.76	V _{TT} + 0.76	16.4	-16.4
SSTL-18 Class I	_	V _{REF} – 0.125	V _{REF} + 0.125	_	_	V _{REF} – 0.25	V _{REF} + 0.25	_	V _{TT} – 0.475	V _{TT} + 0.475	6.7	-6.7
SSTL-18 Class II	_	V _{REF} – 0.125	V _{REF} + 0.125	_	_	V _{REF} – 0.25	V _{REF} + 0.25	_	0.28	V _{CCIO} – 0.28	13.4	-13.4
SSTL-15 Class I	_	V _{REF} – 0.1	V _{REF} + 0.1	_	_	V _{REF} – 0.175	V _{REF} + 0.175	_	$\begin{array}{c} 0.2 \times \\ V_{CCIO} \end{array}$	$\begin{array}{c} 0.8 \times \\ V_{CCIO} \end{array}$	8	-8
SSTL-15 Class II	_	V _{REF} – 0.1	V _{REF} + 0.1	_	_	V _{REF} – 0.175	V _{REF} + 0.175	-	$\begin{array}{c} 0.2 \times \\ V_{CCIO} \end{array}$	$\begin{array}{c} 0.8 \times \\ V_{CCIO} \end{array}$	16	-16
SSTL-135	_	V _{REF} – 0.09	V _{REF} + 0.09	_	_	V _{REF} – 0.16	V _{REF} + 0.16	_	$\begin{array}{c} 0.2 \times \\ V_{\rm CCIO} \end{array}$	$\begin{array}{c} 0.8 \times \\ V_{\rm CCIO} \end{array}$	_	_
HSTL-18 Class I	_	V _{REF} – 0.1	V _{REF} + 0.1	_	_	V _{REF} – 0.2	V _{REF} + 0.2	_	0.4	V _{CCIO} – 0.4	8	-8

 $^{^{(14)}\} V_{TT}$ of transmitting device must track V_{REF} of the receiving device.



I/O Standard	V _{IL(D}	_{C)} (V)	V _{IH(D}	_(C) (V)	V _{IL(A}	_{C)} (V)	V _{IH(A}	_(C) (V)	V _{OL} (V)	V _{OH} (V)	I _{OL} (mA)	I _{OH} (mA)
i/O Staildaid	Min	Max	Min	Max	Min	Max	Min	Max	Max	Min	IOL (IIIA)	IOH (IIIA)
HSTL-18 Class II	_	V _{REF} – 0.1	V _{REF} + 0.1	_	_	V _{REF} - 0.2	$V_{REF} + 0.2$	_	0.4	V _{CCIO} - 0.4	16	-16
HSTL-15 Class I	_	V _{REF} – 0.1	V _{REF} + 0.1	_	_	V _{REF} – 0.2	V _{REF} + 0.2	_	0.4	V _{CCIO} – 0.4	8	-8
HSTL-15 Class II	_	V _{REF} – 0.1	V _{REF} + 0.1	_	_	V _{REF} – 0.2	V _{REF} + 0.2	_	0.4	V _{CCIO} – 0.4	16	-16
HSTL-12 Class I	-0.15	V _{REF} – 0.08	V _{REF} + 0.08	V _{CCIO} + 0.15	-0.24	V _{REF} – 0.15	V _{REF} + 0.15	V _{CCIO} + 0.24	$\begin{array}{c} 0.25 \times \\ V_{\rm CCIO} \end{array}$	$0.75 \times V_{\rm CCIO}$	8	-8
HSTL-12 Class II	-0.15	V _{REF} – 0.08	V _{REF} + 0.08	V _{CCIO} + 0.15	-0.24	V _{REF} – 0.15	V _{REF} + 0.15	V _{CCIO} + 0.24	$\begin{array}{c} 0.25 \times \\ V_{\rm CCIO} \end{array}$	$0.75 \times V_{\rm CCIO}$	14	-14
HSUL-12	_	V _{REF} – 0.13	V _{REF} + 0.13	_	_	V _{REF} – 0.22	V _{REF} + 0.22	_	$\begin{array}{c} 0.1 \times \\ V_{\rm CCIO} \end{array}$	$0.9 \times V_{\rm CCIO}$	_	

Differential SSTL I/O Standards Specifications

Differential SSTL requires a V_{REF} input.

Table 22: Differential SSTL I/O Standards Specifications for MAX 10 Devices—Preliminary

I/O Standard	V _{CCIO} (V)			V _{Swing(DC)} (V)			V _{X(AC)} (V)	V _{Swing(AC)} (V)		
i/O Stailualu	Min	Тур	Max	Min	Max ⁽¹⁷⁾	Min	Тур	Max	Min	Max
SSTL-2 Class I, II	2.375	2.5	2.625	0.36	V _{CCIO}	V _{CCIO} /2 - 0.2	_	V _{CCIO} /2+ 0.2	0.7	V_{CCIO}
SSTL-18 Class I, II	1.7	1.8	1.9	0.25	V _{CCIO}	V _{CCIO} /2 - 0.175	_	V _{CCIO} /2+ 0.175	0.5	V_{CCIO}
SSTL-15 Class I, II	1.425	1.5	1.575	0.2	_	V _{CCIO} /2 - 0.15	_	V _{CCIO} /2 + 0.15	2(V _{IH(AC)} - V _{REF})	$2(V_{IL(AC)} - V_{REF})$

The maximum value for $V_{SWING(DC)}$ is not defined. However, each single-ended signal needs to be within the respective single-ended limits ($V_{IH(DC)}$ and $V_{IL(DC)}$).



I/O Standard	V _{CCIO} (V)			V _{Swing(DC)} (V)			$V_{X(AC)}(V)$		V _{Swing(AC)} (V)		
i/O Staildaid	Min	Тур	Max	Min	Max ⁽¹⁷⁾	Min	Тур	Max	Min	Max	
SSTL-135	1.283	1.35	1.45	0.18	_	V _{REF} – 0.135	$\begin{array}{c} 0.5 \times \\ V_{\rm CCIO} \end{array}$	V _{REF} + 0.135	2(V _{IH(AC)} - V _{REF})	$2(V_{\rm IL(AC)} - V_{\rm REF})$	

Differential HSTL and HSUL I/O Standards Specifications

Differential HSTL requires a V_{REF} input.

Table 23: Differential HSTL and HSUL I/O Standards Specifications for MAX 10 Devices—Preliminary

I/O Standard		V _{CCIO} (V)			V _{DIF(DC)} (V)		V _{X(AC)} (V)			V _{CM(DC)} (V)		
i/O Staildaid	Min	Тур	Max	Min	Max	Min	Тур	Max	Min	Тур	Max	Min
HSTL-18 Class I, II	1.71	1.8	1.89	0.2	_	0.85	_	0.95	0.85	_	0.95	0.4
HSTL-15 Class I, II	1.425	1.5	1.575	0.2	_	0.71	_	0.79	0.71	_	0.79	0.4
HSTL-12 Class I, II	1.14	1.2	1.26	0.16	V _{CCIO}	$\begin{array}{c} 0.48 \times \\ V_{CCIO} \end{array}$	$\begin{array}{c} 0.5 \times \\ V_{\rm CCIO} \end{array}$	$\begin{array}{c} 0.52 \times \\ V_{CCIO} \end{array}$	$\begin{array}{c} 0.48 \times \\ V_{CCIO} \end{array}$	$\begin{array}{c} 0.5 \times \\ V_{\rm CCIO} \end{array}$	$\begin{array}{c} 0.52 \times \\ V_{CCIO} \end{array}$	0.3
HSUL-12	1.14	1.2	1.3	0.26	_	$\begin{array}{c} 0.5 \times \\ V_{\rm CCIO} - \\ 0.12 \end{array}$	$0.5 \times V_{\rm CCIO}$	$\begin{array}{c} 0.5 \times \\ V_{\rm CCIO} + \\ 0.12 \end{array}$	$\begin{array}{c} 0.4 \times \\ V_{\rm CCIO} \end{array}$	$0.5 \times V_{\rm CCIO}$	$0.6 \times V_{\rm CCIO}$	0.44



The maximum value for $V_{SWING(DC)}$ is not defined. However, each single-ended signal needs to be within the respective single-ended limits ($V_{IH(DC)}$ and $V_{IL(DC)}$).

Differential I/O Standards Specifications

Table 24: Differential I/O Standards Specifications for MAX 10 Devices—Preliminary

I/O Standard		V _{CCIO} (V)		V _{ID} (mV)		V _{ICM} (V) ⁽¹⁸⁾		V _{OD} (mV) (19)(20)			V _{OS} (V) ⁽¹⁹⁾		
i/O Standard	Min	Тур	Max	Min	Max	Min	Condition	Max	Min	Тур	Max	Min	Тур	Max
						0.05	$D_{MAX} \le 500 \text{ Mbps}$	1.8						
LVPECL (21)	2.375	2.5	2.625	100	_	0.55	500 Mbps ≤ D _{MAX} ≤ 700 Mbps	1.8	_	_	_	_	_	_
						1.05	D _{MAX} > 700 Mbps	1.55						
						0.05	$D_{MAX} \le 500 \text{ Mbps}$	1.8						
LVDS	2.375	2.5	2.625	100	_	0.55	500 Mbps ≤ D _{MAX} ≤ 700 Mbps	1.8	247	_	600	1.125	1.25	1.375
						1.05	D _{MAX} > 700 Mbps	1.55						
BLVDS (22)	2.375	2.5	2.625	100	_	_	_	_	_	_	_	_	_	_
mini-LVDS	2.375	2.5	2.625	_	_	_	_	_	300	_	600	1	1.2	1.4
RSDS (23)	2.375	2.5	2.625	_	_	_	_	_	100	200	600	0.5	1.2	1.5
PPDS (Row I/Os) (23)	2.375	2.5	2.625	_	_	_	_	_	100	200	600	0.5	1.2	1.4



 $^{^{(18)}~}V_{IN}$ range: 0 V $\leq V_{IN} \leq$ 1.85 V.

⁽¹⁹⁾ R_L range: $90 \le R_L \le 110 \Omega$.

⁽²⁰⁾ Low V_{OD} setting is only supported for RSDS standard.

⁽²¹⁾ LVPECL input standard is only supported at clock input. Output standard is not supported.

No fixed V_{IN}, V_{OD}, and V_{OS} specifications for Bus LVDS (BLVDS). They are dependent on the system topology.

⁽²³⁾ Mini-LVDS, RSDS, and Point-to-Point Differential Signaling (PPDS) standards are only supported at the output pins for MAX 10 devices.

I/O Standard	I/O Standard V _{CCIO} (V)		V _{ID} (mV)		V _{ICM} (V) ⁽¹⁸⁾		V _{OE}	_o (mV) ⁽¹⁹	9)(20)	V _{OS} (V) ⁽¹⁹⁾			
i/O Staildaid	Min	Тур	Max	Min	Max	Min	Condition	Max	Min	Тур	Max	Min	Тур	Max
						0.05	$D_{MAX} \le 500 \text{ Mbps}$	1.8						
TMDS ⁽²⁴⁾	2.375	2.5	2.625	100	_	0.55	500 Mbps ≤ D _{MAX} ≤ 700 Mbps	1.8	_	_	_	_	_	_
						1.05	D _{MAX} > 700 Mbps	1.55						
Sub-LVDS	1.71	1.8	1.89	100	_	0.55	_	1.25		(26)		0.8	0.9	1
SLVS	2.375	2.5	2.625	100	_	0.05	_	1.1		(26)			(27)	
						0.05	D _{MAX} ≤ 500 Mbps	1.8						
HiSpi	2.375	2.5	2.625	100	_	0.55	500 Mbps ≤ D _{MAX} ≤ 700 Mbps	1.8	_	_	_	_	_	_
						1.05	D _{MAX} > 700 Mbps	1.55						

Related Information

MAX 10 LVDS SERDES I/O Standards Support, MAX 10 High-Speed LVDS I/O User Guide

Provides the list of I/O standards supported in single supply and dual supply devices.

Switching Characteristics

This section provides the performance characteristics of MAX 10 core and periphery blocks.



⁽¹⁸⁾ V_{IN} range: $0 \text{ V} \le V_{IN} \le 1.85 \text{ V}$.

⁽¹⁹⁾ R_L range: $90 \le R_L \le 110 \Omega$.

⁽²⁰⁾ Low V_{OD} setting is only supported for RSDS standard.

⁽²⁴⁾ Supported with requirement of an external level shift

⁽²⁵⁾ Sub-LVDS input buffer is using 2.5 V differential buffer.

⁽²⁶⁾ Differential output depends on the values of the external termination resistors.

⁽²⁷⁾ Differential output offset voltage depends on the values of the external termination resistors.

Core Performance Specifications

Clock Tree Specifications

Table 25: Clock Tree Specifications for MAX 10 Devices—Preliminary

Device			Performance			Unit
Device	-16	- C 7	–17	-A7	-C8	Offic
10M02	450	416	416	382	402	MHz
10M04	450	416	416	382	402	MHz
10M08	450	416	416	382	402	MHz
10M16	450	416	416	382	402	MHz
10M25	450	416	416	382	402	MHz
10M40	450	416	416	382	402	MHz
10M50	450	416	416	382	402	MHz

PLL Specifications

Table 26: PLL Specifications for MAX 10 Devices—Preliminary

V_{CCD PLL} should always be connected to V_{CCINT} through decoupling capacitor and ferrite bead.

CCD_I EE	, centi b	1 0 1				
Symbol	Parameter	Condition	Min	Тур	Max	Unit
$f_{\rm IN}$ (28)	Input clock frequency	_	5	_	472.5	MHz
f_{INPFD}	Phase frequency detector (PFD) input frequency	_	5	_	325	MHz
f _{VCO} (29)	PLL internal voltage-controlled oscillator (VCO) operating range	_	600	_	1300	MHz

⁽²⁸⁾ This parameter is limited in the Quartus II software by the I/O maximum frequency. The maximum I/O frequency is different for each I/O standard.



The VCO frequency reported by the Quartus II software in the PLL summary section of the compilation report takes into consideration the VCO post-scale counter κ value. Therefore, if the counter κ has a value of 2, the frequency reported can be lower than the f_{VCO} specification.

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f_{INDUTY}	Input clock duty cycle	_	40	_	60	%
t _{INJITTER_CCJ}	Input clock cycle-to-cycle jitter	F _{INPFD} ≥ 100 MHz	_	_	0.15	UI
(30)	input clock cycle-to-cycle fitter	F _{INPFD} < 100 MHz	_	_	750	ps
f _{OUT_EXT} (28)	PLL output frequency for external clock output	_	_	_	472.5	MHz
		-6 speed grade	_	_	472.5	MHz
f_{OUT}	PLL output frequency to global clock	-7 speed grade	_	_	450	MHz
		-8 speed grade	_	_	402.5	MHz
t _{OUTDUTY}	Duty cycle for external clock output	Duty cycle set to 50%	45	50	55	%
t _{LOCK}	Time required to lock from end of device configuration	_	_	_	1	ms
t _{DLOCK}	Time required to lock dynamically	After switchover, reconfiguring any non-post-scale counters or delays, or when areset is deasserted	_	_	1	ms
toutiitter	Degular I/O paried iittar	F _{OUT} ≥ 100 MHz	_	_	650	ps
t _{outjitter_(31)} Period_io	Regular I/O period jitter	F _{OUT} < 100 MHz	_	_	75	mUI
t _{OUTJITTER_CCJ_}	Pagular I/O gyala ta gyala iittar	F _{OUT} ≥ 100 MHz	_	_	650	ps
IO (31)	Regular I/O cycle-to-cycle jitter	F _{OUT} < 100 MHz	_	_	75	mUI
t _{PLL_PSERR}	Accuracy of PLL phase shift	_	_	_	±50	ps
t _{ARESET}	Minimum pulse width on areset signal.	_	10	_	_	ns

⁽³⁰⁾ A high input jitter directly affects the PLL output jitter. To have low PLL output clock jitter, you must provide a clean clock source, which is less than 200 ps.

Peak-to-peak jitter with a probability level of 10^{-12} (14 sigma, 99.9999999974404% confidence level). The output jitter specification applies to the intrinsic jitter of the PLL, when an input jitter of 30 ps is applied.

Symbol	Parameter	Condition	Min	Тур	Max	Unit
t _{CONFIGPLL}	Time required to reconfigure scan chains for PLLs	_	_	3.5 (32)	_	scanclk cycles
f _{SCANCLK}	scanclk frequency	_	_	_	100	MHz

Table 27: PLL Specifications for MAX 10 Single Supply Devices—Preliminary

For V36 package, the PLL specification is based on single supply devices.

Symbol	Parameter	Condition	Max	Unit
t _{OUTJITTER_PERIOD_} DEDCLK (31)	Dedicated clock output period jitter	$F_{OUT} \ge 100 \text{ MHz}$	660	ps
	Dedicated clock output period fitter	F _{OUT} < 100 MHz	66	mUI
t _{OUTJITTER_CCJ_}	Dedicated clock output cycle-to-cycle jitter	F _{OUT} ≥ 100 MHz	660	ps
toutjitter_ccj_ dedclk ⁽³¹⁾	Dedicated clock output cycle-to-cycle jitter	F _{OUT} < 100 MHz	66	mUI

Table 28: PLL Specifications for MAX 10 Dual Supply Devices—Preliminary

Symbol	Parameter	Condition	Max	Unit
t _{OUTJITTER_} PERIOD_ DEDCLK (31)	Dedicated clock output period jitter	$F_{OUT} \ge 100 \text{ MHz}$	300	ps
	Dedicated clock output period jitter	F _{OUT} < 100 MHz	30	mUI
t _{OUTJITTER_CCJ_} DEDCLK	Dedicated clock output cycle-to-cycle jitter	F _{OUT} ≥ 100 MHz	300	ps
	Dedicated clock output cycle-to-cycle fitter	F _{OUT} < 100 MHz	30	mUI



⁽³²⁾ With 100 MHz scanclk frequency.

Embedded Multiplier Specifications

Table 29: Embedded Multiplier Specifications for MAX 10 Devices—Preliminary

Mode	Number of Multipliers	umber of Multipliers Power Supply Mode		Performance	Unit	
	1 ower Supply Mode		-l6	-C7, -I7, -A7	-C8	Oint
9 × 9-bit multiplier	1	Single supply mode	198	183	160	MHz
9 × 9-oit munipher	1	Dual supply mode	234	212	180	MHz
18 × 18-bit multiplier	1	Single supply mode	198	183	160	MHz
18 × 18-bit munipher	1	Dual supply mode	234	212	180	MHz

Memory Block Performance Specifications

Table 30: Memory Block Performance Specifications for MAX 10 Devices—Preliminary

		Resources Used						
Memory	Mode	LEs	M9K Memory	Power Supply Mode	-16	-C7, -I7, -A7	-C8	Unit
FIFO 256 × 36	EIEO 256 × 26	47	,	Single supply mode	232	219	204	MHz
	47	1	Dual supply mode	284	260	238	MHz	
	Single-port 256 × 36	0	1 -	Single supply mode	232	219	204	MHz
M9K Block				Dual supply mode	284	260	238	MHz
MISK Block	Simple dual-port	0	1	Single supply mode	232	219	204	MHz
	256×36 CLK	0	1	Dual supply mode	284	260	238	MHz
	True dual port	0	1	Single supply mode	232	219	204	MHz
	512 × 18 single СLК	U	1	Dual supply mode	284	260	238	MHz



Internal Oscillator Specifications

Table 31: Internal Oscillator Frequencies for MAX 10 Devices—Preliminary

You can access to the internal oscillator frequencies in this table. The duty cycle of internal oscillator is approximately 45%–55%.

Device	Operating Frequency	Unit
10M02		
10M04		
10M08	55 – 116	MHz
10M16		
10M25		
10M40	35 – 77	MHz
10M50	33 - 77	IVIIIZ

UFM Performance Specifications

Table 32: UFM Performance Specifications for MAX 10 Devices—Preliminary

Plack	Block Mode		Performance	Unit	
DIOCK	Mode	Interface	−l6, −C7, −l7, −A7, −C8	Offit	
UFM	Avalon-MM slave	Parallel	116	MHz	
UFM		Serial		7.25	MHz

ADC Performance Specifications

Single Supply Devices ADC Performance Specifications

Table 33: ADC Performance Specifications for MAX 10 Single Supply Devices—Preliminary

Parameter	Symbol	Condition	Min	Тур	Max	Unit
ADC resolution	_	_	_	_	12	bits



	Parameter	Symbol	Condition	Min	Тур	Max	Unit
ADC supply volta	ge	V _{CC_ONE}	_	2.85	3.0/3.3	3.465	V
External reference	voltage	V _{REF}	_	V _{CC_ONE} - 0.5	_	V _{CC_ONE}	V
Sampling rate		F_S	Accumulative sampling rate	_	_	1	MSPS
Operating junctio	n temperature range	T _J	_	-40	25	125	°C
A nalog input volt	ngo	V _{IN}	Prescalar disabled	0	_	V _{REF}	V
Analog input void	Analog input voltage		Prescalar enabled (33)	0	_	3.6	V
Input resistance		R _{IN}	_	_	(34)	_	kΩ
Input capcitance		C	Dedicated analog input	_	(34)	_	pF
input capettance		C_{IN}	Dual function pin	_	(34)	_	pF
	Offset error and drift	Г	Prescalar disabled	-0.2	_	0.2	%FS
	Offset error and drift	E _{offset}	Prescalar enabled	-0.5	_	0.5	%FS
	C-:	Г	Prescalar disabled	-0.5	_	0.5	%FS
	Gain error and drift	E _{gain}	Prescalar enabled	-0.75	_	0.75	%FS
DC Accuracy	Differential non-linearity	DNL	External V _{REF} , no missing code	-0.9	_	0.9	LSB
	Differential non linearity	DNL	Internal V _{REF} , no missing code	-1	_	1.7	LSB
	Integral non linearity	INL	_	-2	_	2	LSB



Prescalar function divides the analog input voltage by half. The analog input handles up to 3.6 V for the MAX 10 single supply devices.
Refer to the MAX 10 Analog-to-Digital Converter User Guide for the RC equation.

P	arameter	Symbol	Condition	Min	Тур	Max	Unit
	Total harmonic distortion	THD	F_{IN} = 50 kHz, F_S = 1 MHz, PLL	-65 ⁽³⁵⁾	_	_	dB
AC Accuracy	Signal-to-noise ratio	SNR	F_{IN} = 50 kHz, F_S = 1 MHz, PLL	54 (36)	_	_	dB
	Signal-to-noise and distortion	SINAD	$F_{IN} = 50 \text{ kHz}, F_S = 1$ MHz, PLL	53 (37)	_	_	dB
On-Chip Tempera- ture Sensor	Temperature sampling rate	T_S	_	_	_	50	kSPS
	Absolute accuracy	_	-40 to 125°C, with 64 samples averaging	_	_	±10	°C
			Single measurement	_	_	1	Cycle
Conversion Rate (39)	Conversion time	_	Continuous measurement	_	_	1	Cycle
			Temperature measurement	_	_	1	Cycle

Related Information

Guidelines: Board Design for Analog Input, MAX 10 Analog-to-Digital Converter User Guide

Provides more information about the conversion rate and RC equation.



 $^{^{(35)}}$ THD with prescalar enabled is 6dB less than the specification.

⁽³⁶⁾ SNR with prescalar enabled is 6dB less than the specification.

⁽³⁷⁾ SINAD with prescalar enabled is 6dB less than the specification.

⁽³⁸⁾ For the Quartus II software version 15.0 and later, Altera Modular ADC and Altera Modular Dual ADC IP cores handle the 64 samples averaging. For the Quartus II software versions prior to 14.1, you need to implement your own averaging calculation.

⁽³⁹⁾ For more detailed description, refer to Timing section in the MAX 10 Analog-to-Digital Converter User Guide.

Dual Supply Devices ADC Performance Specifications

Table 34: ADC Performance Specifications for MAX 10 Dual Supply Devices—Preliminary

Parameter	Symbol	Condition	Min	Тур	Max	Unit
ADC resolution	_	_	_	_	12	bits
Analog supply voltage	V _{CCA_ADC}	_	2.375	2.5	2.625	V
Digital supply voltage	V _{CCINT}	_	1.15	1.2	1.25	V
External reference voltage	V _{REF}	_	V _{CCA_ADC} - 0.5		V _{CCA_ADC}	V
Sampling rate	F_S	Accumulative sampling rate	_	_	1	MSPS
Operating junction temperature range	T _J	_	-40	25	125	°C
Analog input voltage	37	Prescalar disabled	0	_	V _{REF}	V
Analog input voltage	V_{IN}	Prescalar enabled (40)	0	_	3	V
Analog supply current (DC)	I _{ACC_ADC}	Average current	_	275	450	μΑ
Digital supply current (DC)	I _{CCINT}	Average current	_	65	150	μΑ
Input resistance	R _{IN}	_	_	(41)	_	kΩ
Input capcitance	$C_{ m IN}$	Dedicated analog input	_	(41)	_	pF
		Dual function pin	_	(41)	_	pF



 $^{^{(40)}}$ Prescalar function divides the analog input voltage by half. The analog input handles up to 3 V input for the MAX 10 dual supply devices. Refer to the MAX 10 Analog-to-Digital Converter User Guide for the RC equation.

	Parameter	Symbol	Condition	Min	Тур	Max	Unit
	Offset error and drift	E	Prescalar disabled	-0.2	_	0.2	%FS
DC Accuracy	Offset error and drift	E _{offset}	Prescalar enabled	-0.5	_	0.5	%FS
	Gain error and drift	E	Prescalar disabled	-0.5	_	0.5	%FS
	Gain error and drift	$\mathrm{E}_{\mathrm{gain}}$	Prescalar enabled	-0.75	_	0.75	%FS
	Differential non linearity	DNL	External V _{REF} , no missing code	-0.9	_	0.9	LSB
	Differential floir fifearity		Internal V _{REF} , no missing code	-1	_	1.7	LSB
	Integral non linearity	INL	_	-2	_	2	LSB
AC Accuracy	Total harmonic distortion	THD	$F_{IN} = 50 \text{ kHz}, F_S = 1$ MHz, PLL	-70 (42)(43)	_	_	dB
	Signal-to-noise ratio	SNR	$F_{IN} = 50 \text{ kHz}, F_S = 1$ MHz, PLL	62 (44)(45)		_	dB
	Signal-to-noise and distortion	SINAD	$F_{IN} = 50 \text{ kHz}, F_S = 1$ MHz, PLL	61.5 (46)(47)	_	_	dB



 $^{^{\}rm (42)}\,$ Total harmonic distortion is –65 dB for dual function pin.

⁽⁴³⁾ THD with prescalar enabled is 6dB less than the specification.

⁽⁴⁴⁾ Signal-to-noise ratio is 54 dB for dual function pin.

⁽⁴⁵⁾ SNR with prescalar enabled is 6dB less than the specification.

⁽⁴⁶⁾ Signal-to-noise and distortion is 53 dB for dual function pin.

⁽⁴⁷⁾ SINAD with prescalar enabled is 6dB less than the specification.

Р	Parameter		Condition	Min	Тур	Max	Unit
	Temperature sampling rate	T_{S}	_	_	_	50	kSPS
On-Chip Tempera- ture Sensor	Absolute accuracy	_	-40 to 125°C, with 64 samples averaging	_	_	±5	°C
			Single measurement	_	_	1	Cycle
Conversion Rate (49)	Conversion time	_	Continuous measurement	_	_	1	Cycle
			Temperature measurement	_	_	1	Cycle

Related Information

Guidelines: Board Design for Analog Input, MAX 10 Analog-to-Digital Converter User Guide

Provides more information about the conversion rate and RC equation.

Periphery Performance Specifications

This section describes the periphery performance, high-speed I/O, and external memory interface.

Actual achievable frequency depends on design and system specific factors. Ensure proper timing closure in your design and perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specifications

For more information about the high-speed and low-speed I/O performance pins, refer to the respective device pin-out files.

Related Information

Documentation: Pin-Out Files for Altera Devices



⁽⁴⁸⁾ For the Quartus II software version 15.0 and later, Altera Modular ADC and Altera Modular Dual ADC IP cores handle the 64 samples averaging. For the Quartus II software versions prior to 14.1, you need to implement your own averaging calculation.

⁽⁴⁹⁾ For more detailed description, refer to Timing section in the MAX 10 Analog-to-Digital Converter User Guide.

$True\ PPDS\ and\ Emulated\ PPDS_E_3R\ Transmitter\ Timing\ Specifications$

Table 35: True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices—Preliminary

True **PPDS** transmitter is only supported at bottom I/O banks. Emulated **PPDS** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	−l6, −C7, −l7			-A7				Unit		
Зуппроі			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
		×10	5	_	155	5	_	155	5	_	155	MHz
	Input clock	×8	5	_	155	5	_	155	5	_	155	MHz
f	frequency (high-	×7	5	_	155	5	_	155	5	_	155	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	155	5	_	155	5	_	155	MHz
	performance pin)	×2	5	_	155	5	_	155	5	_	155	MHz
		×1	5	_	310	5	_	310	5	_	310	MHz
	Data rate (high- speed I/O performance pin)	×10	100	_	310	100	_	310	100	_	310	Mbps
		×8	80	_	310	80	_	310	80	_	310	Mbps
HSIODR		×7	70	_	310	70	_	310	70	_	310	Mbps
HOIODK		×4	40	_	310	40	_	310	40	_	310	Mbps
		×2	20	_	310	20	_	310	20	_	310	Mbps
		×1	10	_	310	10	_	310	10	_	310	Mbps
		×10	5	_	150	5	_	150	5	_	150	MHz
	Input clock	×8	5	_	150	5	_	150	5	_	150	MHz
f	frequency (low-	×7	5	_	150	5	_	150	5	_	150	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	150	5	_	150	5	_	150	MHz
	periormance pm)	×2	5	_	150	5	_	150	5	_	150	MHz
		×1	5	_	300	5	_	300	5	_	300	MHz



Symbol	Parameter	Mode	−l6, −C7, −l7				-A7			- Unit		
Зуппоот		Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
		×10	100	_	300	100	_	300	100	_	300	Mbps
		×8	80	_	300	80	_	300	80	_	300	Mbps
HSIODR	Data rate (low- speed I/O	×7	70	_	300	70	_	300	70	_	300	Mbps
HOLDK	performance pin)	×4	40	_	300	40	_	300	40	_	300	Mbps
		×2	20	_	300	20	_	300	20	_	300	Mbps
		×1	10	_	300	10	_	300	10	_	300	Mbps
t_{DUTY}	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%
TCCS ⁽⁵⁰⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps
÷ (51)	Output jitter (high- speed I/O performance pin)	_	_	_	425	_	_	425	_	_	425	ps
t _{x Jitter} ⁽⁵¹⁾	Output jitter (low- speed I/O performance pin)	_	_	_	470	_	_	470	_	_	470	ps
t _{RISE}	Rise time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
$t_{ m FALL}$	Fall time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps



 $^{^{(50)}\,}$ TCCS specifications apply to I/O banks from the same side only.

⁽⁵¹⁾ TX jitter is the jitter induced from core noise and I/O switching noise.

Symbol	Parameter	Mode	−l6, −C7, −l7			-A7			-C8			- Unit
Syllibol			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
t_{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	_	_	1	ms

True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications

Table 36: True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices—Preliminary

True **RSDS** transmitter is only supported at bottom I/O banks. Emulated **RSDS** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	−l6, −C7, −l7			-A7			-C8			Unit
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
	Input clock frequency (high- speed I/O performance pin)	×10	5	_	155	5	_	155	5	_	155	MHz
		×8	5	_	155	5	_	155	5	_	155	MHz
f		×7	5	_	155	5	_	155	5	_	155	MHz
f _{HSCLK}		×4	5	_	155	5	_	155	5	_	155	MHz
		×2	5	_	155	5	_	155	5	_	155	MHz
		×1	5	_	310	5	_	310	5	_	310	MHz



Symbol	Parameter	Mode	−l6, −C7, −l7				-A7		-C8			- Unit
Symbol			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	- Onit
		×10	100	_	310	100	_	310	100	_	310	Mbps
		×8	80	_	310	80	_	310	80	_	310	Mbps
HSIODR	Data rate (high- speed I/O	×7	70	_	310	70	_	310	70	_	310	Mbps
HSIODK	performance pin)	×4	40	_	310	40	_	310	40	_	310	Mbps
		×2	20	_	310	20	_	310	20	_	310	Mbps
		×1	10	_	310	10	_	310	10	_	310	Mbps
	Input clock frequency (low- speed I/O performance pin)	×10	5	_	150	5	_	150	5	_	150	MHz
		×8	5	_	150	5	_	150	5	_	150	MHz
f		×7	5	_	150	5	_	150	5	_	150	MHz
f_{HSCLK}		×4	5	_	150	5	_	150	5	_	150	MHz
		×2	5	_	150	5	_	150	5	_	150	MHz
		×1	5	_	300	5	_	300	5	_	300	MHz
		×10	100	_	300	100	_	300	100	_	300	Mbps
		×8	80	_	300	80	_	300	80	_	300	Mbps
HSIODR	Data rate (low- speed I/O	×7	70	_	300	70	_	300	70	_	300	Mbps
HSIODK	performance pin)	×4	40	_	300	40	_	300	40	_	300	Mbps
		×2	20	_	300	20	_	300	20	_	300	Mbps
		×1	10	_	300	10	_	300	10	_	300	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%



Symbol	Parameter	Mode	-	-l6, –C7, –l	7		-A7			-C8		Unit
Syllibol	raiailletei	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
TCCS ⁽⁵²⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps
t _{x Jitter} (53)	Output jitter (high- speed I/O performance pin)	_	_	_	425	_	_	425	_	_	425	ps
x Jitter	Output jitter (low- speed I/O performance pin)	_	_	_	470	_	_	470	_	_	470	ps
t_{RISE}	Rise time	$20 - 80\%,$ $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
t_{FALL}	Fall time	$20 - 80\%$, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	_	_	1	ms



TCCS specifications apply to I/O banks from the same side only.
 TX jitter is the jitter induced from core noise and I/O switching noise.

Emulated RSDS_E_1R Transmitter Timing Specifications

Table 37: Emulated RSDS_E_1R Transmitter Timing Specifications for MAX 10 Dual Supply Devices—Preliminary

Emulated RSDS_E_1R transmitter is supported at the output pin of all I/O banks.

Symbol	Davameter	Mode	-	-I6, –C7, –I	7		-A7			-C8		Unit
Symbol	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
		×10	5	_	85	5	_	85	5	_	85	MHz
	Input clock	×8	5	_	85	5	_	85	5	_	85	MHz
f	frequency (high-	×7	5	_	85	5	_	85	5	_	85	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	85	5	_	85	5	_	85	MHz
	periormance pm)	×2	5	_	85	5	_	85	5	_	85	MHz
		×1	5	_	170	5	_	170	5	_	170	MHz
		×10	100	_	170	100	_	170	100	_	170	Mbps
		×8	80	_	170	80	_	170	80	_	170	Mbps
HSIODR	Data rate (high- speed I/O	×7	70	_	170	70	_	170	70	_	170	Mbps
HSIODK	performance pin)	×4	40		170	40		170	40		170	Mbps
		×2	20	_	170	20	_	170	20	_	170	Mbps
		×1	10	_	170	10	_	170	10	_	170	Mbps
		×10	5		85	5		85	5		85	MHz
	Input clock	×8	5	_	85	5	_	85	5	_	85	MHz
£	frequency (low-	×7	5	_	85	5	_	85	5	_	85	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	85	5	_	85	5	_	85	MHz
	periormance pm)	×2	5	_	85	5	_	85	5	_	85	MHz
		×1	5	_	170	5	_	170	5	_	170	MHz



Symbol	Parameter	Mode	-	-l6, –C7, –l	7		-A7			-C8		Unit
Зуппон	raiailletei	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
		×10	100	_	170	100	_	170	100	_	170	Mbps
		×8	80	_	170	80	_	170	80	_	170	Mbps
HSIODR	Data rate (low- speed I/O	×7	70	_	170	70	_	170	70	_	170	Mbps
Holobk	performance pin)	×4	40	_	170	40	_	170	40	_	170	Mbps
		×2	20	_	170	20	_	170	20	_	170	Mbps
		×1	10	_	170	10	_	170	10	_	170	Mbps
$t_{ m DUTY}$	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%
TCCS ⁽⁵⁴⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps
4 (55)	Output jitter (high- speed I/O performance pin)	_	_	_	425	_	_	425	_	_	425	ps
t _{x Jitter} (55)	Output jitter (low- speed I/O performance pin)	_	_	_	470	_	_	470	_	_	470	ps
t _{RISE}	Rise time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_		500	_	ps
t_{FALL}	Fall time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps



TCCS specifications apply to I/O banks from the same side only.
 TX jitter is the jitter induced from core noise and I/O switching noise.

Symbol	Parameter	Mode	-	-l6, –C7, –l	7		-A7			-C8		Unit
Symbol	raiailletei	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	_	_	1	ms

True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications

Table 38: True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices—Preliminary

True **mini-LVDS** transmitter is only supported at the bottom I/O banks. Emulated **mini-LVDS_E_3R** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	-	-l6, –C7, –l	7		-A7			− C 8		Unit
Зуппоот	raiametei	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
		×10	5	_	155	5	_	155	5	_	155	MHz
Input clock	Input alock	×8	5	_	155	5	_	155	5	_	155	MHz
£	frequency (high-	×7	5	_	155	5	_	155	5	_	155	MHz
$t_{ m HSCLK}$	speed I/O performance pin)	×4	5	_	155	5	_	155	5	_	155	MHz
	performance pm)	×2	5	_	155	5	_	155	5	_	155	MHz
		×1	5	_	310	5	_	310	5	_	310	MHz



Cumbal	Parameter	Mode	-	-l6, –C7, –l	7		-A7			-C8		Unit
Symbol	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
		×10	100	_	310	100	_	310	100	_	310	Mbps
		×8	80	_	310	80	_	310	80	_	310	Mbps
HSIODR	Data rate (high- speed I/O	×7	70	_	310	70	_	310	70	_	310	Mbps
пзюрк	performance pin)	×4	40	_	310	40	_	310	40	_	310	Mbps
		×2	20	_	310	20	_	310	20	_	310	Mbps
		×1	10	_	310	10	_	310	10	_	310	Mbps
		×10	5	_	150	5	_	150	5	_	150	MHz
	Input clock	×8	5	_	150	5	_	150	5	_	150	MHz
f	frequency (low-	×7	5	_	150	5	_	150	5	_	150	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	150	5	_	150	5	_	150	MHz
	periormance pm)	×2	5	_	150	5	_	150	5	_	150	MHz
		×1	5	_	300	5	_	300	5	_	300	MHz
		×10	100	_	300	100	_	300	100	_	300	Mbps
		×8	80	_	300	80	_	300	80	_	300	Mbps
HSIODR	Data rate (low- speed I/O	×7	70	_	300	70	_	300	70	_	300	Mbps
HSIODK	performance pin)	×4	40	_	300	40	_	300	40	_	300	Mbps
		×2	20	_	300	20	_	300	20	_	300	Mbps
		×1	10	_	300	10	_	300	10	_	300	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%



Symbol	Davameter	Mode	-	-l6, –C7, –l	7		-A7			-C8		Unit
Зушьог	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
TCCS ⁽⁵⁶⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps
t _{x Jitter} (57)	Output jitter (high- speed I/O performance pin)	_	_	_	425	_	_	425	_	_	425	ps
^t x Jitter	Output jitter (low- speed I/O performance pin)	_	_	_	470	_	_	470	_	_	470	ps
t_{RISE}	Rise time	$20 - 80\%$, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
t_{FALL}	Fall time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	_	_	1	ms



 $^{^{(56)}\,}$ TCCS specifications apply to I/O banks from the same side only.

⁽⁵⁷⁾ TX jitter is the jitter induced from core noise and I/O switching noise.

True LVDS Transmitter Timing

Single Supply Devices True LVDS Transmitter Timing Specifications

Table 39: True LVDS Transmitter Timing Specifications for MAX 10 Single Supply Devices—Preliminary

True **LVDS** transmitter is only supported at the bottom I/O banks.

Symbol	Parameter	Mode		−C7, −I7			-A7			-C8		Unit
Зушьог	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
		×10	5	_	145	5	_	100	5	_	100	MHz
		×8	5	_	145	5	_	100	5	_	100	MHz
£	Input clock	×7	5	_	145	5	_	100	5	_	100	MHz
f_{HSCLK}	frequency	×4	5	_	145	5	_	100	5	_	100	MHz
		×2	5	_	145	5	_	100	5	_	100	MHz
		×1	5	_	290	5	_	200	5	_	200	MHz
		×10	100	_	290	100	_	200	100	_	200	Mbps
		×8	80	_	290	80	_	200	80	_	200	Mbps
HSIODR	Data rate	×7	70	_	290	70	_	200	70	_	200	Mbps
HSIODK	Data fate	×4	40	_	290	40	_	200	40	_	200	Mbps
		×2	20	_	290	20	_	200	20	_	200	Mbps
		×1	10	_	290	10	_	200	10	_	200	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%
TCCS ⁽⁵⁸⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps

⁽⁵⁸⁾ TCCS specifications apply to I/O banks from the same side only.



Symbol	Darameter	Mode		-C7, -I7			-A7			-C8		Unit
Symbol	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
t _{x Jitter} (59)	Output jitter	_	_	_	1,000	_	_	1,000	_	_	1,000	ps
$t_{ m RISE}$	Rise time	20 – 80%, C _{LOAD} = 5 pF	_	500	_	_	500	_	_	500	_	ps
$t_{ m FALL}$	Fall time	20 – 80%, C _{LOAD} = 5 pF	_	500	_	_	500	_	_	500	_	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	-	_	1	ms



 $^{^{(59)}\,}$ TX jitter is the jitter induced from core noise and I/O switching noise.

Dual Supply Devices True LVDS Transmitter Timing Specifications

Table 40: True LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices—Preliminary

True LVDS transmitter is only supported at the bottom I/O banks.

Symbol	Parameter	Mode	-	-16, –C7, –	17		-A7			-C8		Unit
Зуппоот	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
		×10	5	_	360 ⁽⁶⁰⁾ , 335 ⁽⁶¹⁾	5	_	310	5	_	300	MHz
		×8	5	_	360	5	_	320	5	_	320	MHz
f_{HSCLK}	Input clock frequency	×7	5	_	360 ⁽⁶⁰⁾ , 335 ⁽⁶¹⁾	5	_	310	5	_	300	MHz
		×4	5	_	360	5	_	320	5	_	320	MHz
		×2	5	_	360	5	_	320	5	_	320	MHz
		×1	5	_	360	5	_	320	5	_	320	MHz
		×10	100	_	720 ⁽⁶⁰⁾ , 670 ⁽⁶¹⁾	100	_	620	100	_	600	Mbps
		×8	80	_	720	80	_	640	80	_	640	Mbps
HSIODR	Data rate	×7	70	_	720 ⁽⁶⁰⁾ , 670 ⁽⁶¹⁾	70	_	620	70	_	600	Mbps
		×4	40	_	720	40	_	640	40	_	640	Mbps
		×2	20	_	720	20	_	640	20	_	640	Mbps
		×1	10	_	360	10	_	320	10	_	320	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%

Applicable to –I6 speed grade.



⁽⁶¹⁾ Applicable to -C7 and -I7 speed grades.

Symbol	Parameter	Mode	-	·l6, –C7, –l	7		-A7			-C8		Unit
Зуппрог	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
TCCS ⁽⁶²⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps
t _{x Jitter} ⁽⁶³⁾	Output jitter	_	_	_	380	_	_	380	_	_	380	ps
$t_{ m RISE}$	Rise time	20 – 80%, C _{LOAD} = 5 pF	_	500	_	_	500	_	_	500	_	ps
$t_{ m FALL}$	Fall time	20 – 80%, C _{LOAD} = 5 pF	_	500	_	_	500	_	_	500	_	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	_	_	1	ms



 $^{^{(62)}\,}$ TCCS specifications apply to I/O banks from the same side only.

⁽⁶³⁾ TX jitter is the jitter induced from core noise and I/O switching noise.

Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications

Single Supply Devices Emulated LVDS_E_3R Transmitter Timing Specifications

Table 41: Emulated LVDS_E_3R Transmitter Timing Specifications for MAX 10 Single Supply Devices—Preliminary

Emulated LVDS_E_3R transmitters are supported at the output pin of all I/O banks.

Symbol	Parameter	Mode		-C7, -I7			-A7			-C8		Unit
Symbol	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Onit
		×10	5	_	142.5	5	_	100	5	_	100	MHz
	Input clock	×8	5	_	142.5	5	_	100	5	_	100	MHz
f	frequency (high-	×7	5	_	142.5	5	_	100	5	_	100	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	142.5	5	_	100	5	_	100	MHz
	periormanee pm)	×2	5	_	142.5	5	_	100	5	_	100	MHz
		×1	5	_	285	5	_	200	5	_	200	MHz
		×10	100	_	285	100	_	200	100	_	200	Mbps
		×8	80	_	285	80	_	200	80	_	200	Mbps
HSIODR	Data rate (high- speed I/O	×7	70	_	285	70	_	200	70	_	200	Mbps
HSIODK	performance pin)	×4	40	_	285	40	_	200	40	_	200	Mbps
		×2	20	_	285	20	_	200	20	_	200	Mbps
		×1	10	_	285	10	_	200	10	_	200	Mbps
		×10	5	_	100	5	_	100	5	_	100	MHz
	Immut alo als	×8	5	_	100	5	_	100	5	_	100	MHz
£	Input clock frequency (low-	×7	5	_	100	5	_	100	5	_	100	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	100	5	_	100	5	_	100	MHz
	periormance pm)	×2	5	_	100	5	_	100	5	_	100	MHz
		×1	5	_	200	5	_	200	5	_	200	MHz



Symbol	Parameter	Mode		−C7, −I7		-A7			-C8			Unit
Symbol	Parameter	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
		×10	100	_	200	100	_	200	100	_	200	Mbps
		×8	80	_	200	80	_	200	80	_	200	Mbps
HSIODR	Data rate (low- speed I/O	×7	70	_	200	70	_	200	70	_	200	Mbps
HSIODK	performance pin)	×4	40	_	200	40	_	200	40	_	200	Mbps
		×2	20	_	200	20	_	200	20	_	200	Mbps
		×1	10	_	200	10	_	200	10	_	200	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%
TCCS ⁽⁶⁴⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps
t _{x Jitter} (65)	Output jitter	_	_	_	1,000	_	_	1,000	_	_	1,000	ps
t_{RISE}	Rise time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
t_{FALL}	Fall time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	_	_	1	ms

 $^{^{(64)}}$ TCCS specifications apply to I/O banks from the same side only.



⁽⁶⁵⁾ TX jitter is the jitter induced from core noise and I/O switching noise.

Dual Supply Devices Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications

Table 42: Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices—Preliminary

Emulated LVDS_E_3R, SLVS, and Sub-LVDS transmitters are supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	-	-l6, –C7, –l	7	-A7			-C8			Unit
Syllibol	rafailletei	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
		×10	5	_	300	5	_	275	5	_	275	MHz
	T	×8	5	_	300	5	_	275	5	_	275	MHz
£	Input clock frequency (high-	×7	5	_	300	5	_	275	5	_	275	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	300	5	_	275	5	_	275	MHz
	performance pm)	×2	5	_	300	5	_	275	5	_	275	MHz
		×1	5	_	300	5	_	275	5	_	275	MHz
		×10	100	_	600	100	_	550	100	_	550	Mbps
		×8	80	_	600	80	_	550	80	_	550	Mbps
HSIODR	Data rate (high- speed I/O	×7	70	_	600	70	_	550	70	_	550	Mbps
HSIODK	performance pin)	×4	40	_	600	40	_	550	40	_	550	Mbps
		×2	20	_	600	20	_	550	20	_	550	Mbps
		×1	10	_	300	10	_	275	10	_	275	Mbps
		×10	5	_	150	5	_	150	5	_	150	MHz
	Input clock	×8	5	_	150	5	_	150	5	_	150	MHz
f	frequency (low-	×7	5	_	150	5	_	150	5	_	150	MHz
f_{HSCLK}	speed I/O performance pin)	×4	5	_	150	5	_	150	5	_	150	MHz
	periormance pm)	×2	5	_	150	5	_	150	5	_	150	MHz
		×1	5	_	300	5	_	300	5	_	300	MHz



Symbol	Parameter	Mode	-l6, -C7, -l7		-A7			-C8			Unit	
Зуппон	raiailletei	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
		×10	100	_	300	100	_	300	100	_	300	Mbps
		×8	80	_	300	80	_	300	80	_	300	Mbps
HSIODR	Data rate (low- speed I/O	×7	70	_	300	70	_	300	70	_	300	Mbps
HOIODK	performance pin)	$\times 4$	40	_	300	40	_	300	40	_	300	Mbps
		×2	20	_	300	20	_	300	20	_	300	Mbps
		×1	10	_	300	10	_	300	10	_	300	Mbps
$t_{ m DUTY}$	Duty cycle on transmitter output clock	_	45	_	55	45	_	55	45	_	55	%
TCCS ⁽⁶⁶⁾	Transmitter channel-to-channel skew	_	_	_	410	_	_	410	_	_	410	ps
+ (67)	Output jitter (high- speed I/O performance pin)	_	_	_	425	_	_	425	_	_	425	ps
t _{x Jitter} (67)	Output jitter (low- speed I/O performance pin)	_	_	_	470	_	_	470	_	_	470	ps
t _{RISE}	Rise time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps
t_{FALL}	Fall time	20 - 80%, $C_{LOAD} = 5 \text{ pF}$	_	500	_	_	500	_	_	500	_	ps



 $^{^{(66)}\,}$ TCCS specifications apply to I/O banks from the same side only.

⁽⁶⁷⁾ TX jitter is the jitter induced from core noise and I/O switching noise.

Symbol	Parameter	Mode	-	-I6, –C7, –I	7		-A7			-C8		Unit
Syllibol	raiailletei	Mode	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Offic
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	_	1	_	_	1	_	_	1	ms

LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications

Single Supply Devices LVDS Receiver Timing Specifications

Table 43: LVDS Receiver Timing Specifications for MAX 10 Single Supply Devices—Preliminary

LVDS receivers are supported at all banks.

Symbol	Parameter	Mode	-C7	′, –I7	-,	A 7	-(C8	Unit
Зуппоот	raiailletei	Mode	Min	Max	Min	Max	Min	Max	Onic
		×10	5	145	5	100	5	100	MHz
		×8	5	145	5	100	5	100	MHz
ť	Input clock frequency (high-speed I/O	×7	5	145	5	100	5	100	MHz
f_{HSCLK}	performance pin)	×4	5	145	5	100	5	100	MHz
		×2	5	145	5	100	5	100	MHz
		×1	5	290	5	200	5	200	MHz



Symbol	Parameter	Mode	-C7	7, –17	-	A7	-	C8	Unit
Зушьог	Parameter	Mode	Min	Max	Min	Max	Min	Max	Onit
		×10	100	290	100	200	100	200	Mbps
		×8	80	290	80	200	80	200	Mbps
HSIODR	Data rate (high-speed I/	×7	70	290	70	200	70	200	Mbps
пзюрк	O performance pin)	×4	40	290	40	200	40	200	Mbps
		×2	20	290	20	200	20	200	Mbps
		×1	10	290	10	200	10	200	Mbps
		×10	5	100	5	100	5	100	MHz
		×8	5	100	5	100	5	100	MHz
ç	Input clock frequency (low-speed I/O	×7	5	100	5	100	5	100	MHz
f_{HSCLK}	performance pin)	×4	5	100	5	100	5	100	MHz
		×2	5	100	5	100	5	100	MHz
		×1	5	200	5	200	5	200	MHz
		×10	100	200	100	200	100	200	Mbps
		×8	80	200	80	200	80	200	Mbps
HSIODR	Data rate (low-speed I/	×7	70	200	70	200	70	200	Mbps
пзюрк	O performance pin)	×4	40	200	40	200	40	200	Mbps
		×2	20	200	20	200	20	200	Mbps
		×1	10	200	10	200	10	200	Mbps
SW	Sampling window (high-speed I/O performance pin)	_	_	800	_	800	_	800	ps
3	Sampling window (low- speed I/O performance pin)	_	_	1,000	_	1,000	_	1,000	ps



Symbol	Parameter	Mode	–C7, –I7		-A7		-C8		Unit
39111001	raiailletei	Mode	Min	Max	Min	Max	Min	Max	Offic
t _{x Jitter} (68)	Input jitter	_	_	1,000	_	1,000	_	1,000	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	1	_	1	_	1	ms

Dual Supply Devices LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications

Table 44: LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for MAX 10 Dual Supply Devices—Preliminary

LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS receivers are supported at all banks.

Symbol	Parameter	er Mode		–l6, –C7, –l7 Mode		4 7	-(C8	- Unit	
Зуппоп	raiametei	Mode	Min	Max	Min	Max	Min	Max	Offic	
		×10	5	360	5	320	5	320	MHz	
		×8	5	360	5	320	5	320	MHz	
f	Input clock frequency (high-speed I/O	×7	5	360	5	320	5	320	MHz	
f _{HSCLK}	performance pin)	×4	5	360	5	320	5	320	MHz	
		×2	5	360	5	320	5	320	MHz	
		×1	5	360	5	320	5	320	MHz	



⁽⁶⁸⁾ TX jitter is the jitter induced from core noise and I/O switching noise.

Symbol	Parameter	Mode	-l6, -	C7, –I7	-/	A 7	-C8		Unit
Зушьог	Parameter	Mode	Min	Max	Min	Max	Min	Max	Onit
		×10	100	720	100	640	100	640	Mbps
		×8	80	720	80	640	80	640	Mbps
HSIODR	Data rate (high-speed I/	×7	70	720	70	640	70	640	Mbps
пыорк	O performance pin)	×4	40	720	40	640	40	640	Mbps
		×2	20	720	20	640	20	640	Mbps
		×1	10	360	10	320	10	320	Mbps
		×10	5	150	5	150	5	150	MHz
		×8	5	150	5	150	5	150	MHz
f	Input clock frequency (low-speed I/O	×7	5	150	5	150	5	150	MHz
f_{HSCLK}	performance pin)	×4	5	150	5	150	5	150	MHz
		×2	5	150	5	150	5	150	MHz
		×1	5	300	5	300	5	300	MHz
		×10	100	300	100	300	100	300	Mbps
		×8	80	300	80	300	80	300	Mbps
HSIODR	Data rate (low-speed I/	×7	70	300	70	300	70	300	Mbps
HSIODK	O performance pin)	×4	40	300	40	300	40	300	Mbps
		×2	20	300	20	300	20	300	Mbps
		×1	10	300	10	300	10	300	Mbps
SW	Sampling window	_	_	400	_	400	_	400	ps
t _{x Jitter} (69)	Input jitter	_	_	500	_	500	_	500	ps



⁽⁶⁹⁾ TX jitter is the jitter induced from core noise and I/O switching noise.

Symbol	Parameter	Mode	-16, -0	C7, –I7	-1	4 7	-(C8	Unit
Зуппоот	raiailletei	Mode	Min	Max	Min	Max	Min	Max	Offic
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	_	_	1	_	1	_	1	ms

Memory Output Clock Jitter Specifications

MAX 10 devices support external memory interfaces up to 303 MHz. The external memory interfaces for MAX 10 devices calibrate automatically.

The memory output clock jitter measurements are for 200 consecutive clock cycles.

The clock jitter specification applies to memory output clock pins generated using DDIO circuits clocked by a PLL output routed on a PHY clock network.

DDR3 and LPDDR2 SDRAM memory interfaces are only supported on the fast speed grade device.

Table 45: Memory Output Clock Jitter Specifications for MAX 10 Devices—Preliminary

Parameter	Symbol	−6 Spee	d Grade	–7 Spee	d Grade	Unit
r al allietei	Зуппоот	Min	Max	Min	Max	Offic
Clock period jitter	t _{JIT(per)}	-100	100	-125	125	ps
Cycle-to-cycle period jitter	t _{JIT(cc)}	_	200	_	250	ps

Related Information

Literature: External Memory Interfaces

Provides more information about external memory system performance specifications, board design guidelines, timing analysis, simulation, and debugging information.

Configuration Specifications

This section provides configuration specifications and timing for MAX 10 devices.



JTAG Timing Parameters

Table 46: JTAG Timing Parameters for MAX 10 Devices—Preliminary

The values are based on $C_L = 10 \text{ pF}$ of TDO .

The affected Boundary Scan Test (BST) instructions are SAMPLE/PRELOAD, EXTEST, INTEST, and CHECK_STATUS.

Symbol	Parameter	Non-BST and non	-CONFIG_IO Operation	BST and CO	ONFIG_IO Operation	Unit
Зуппоот	raiametei	Minimum	Maximum	Minimum	Maximum	Offic
t_{JCP}	тск clock period	40	_	50	_	ns
t _{JCH}	тск clock high time	20	_	25	_	ns
t_{JCL}	тск clock low time	20	_	25	_	ns
t _{JPSU_TDI}	JTAG port setup time	2	_	2	_	ns
t _{JPSU_TMS}	JTAG port setup time	3	_	3	_	ns
t _{JPH}	JTAG port hold time	10	_	10	_	ns
t _{JPCO}	JTAG port clock to output	_	 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) 17 (for V_{CCIO} = 1.8 and 1.5 V) 	_	• 18 (for V _{CCIO} = 3.3, 3.0, and 2.5 V) • 20 (for V _{CCIO} = 1.8 and 1.5 V)	ns
t _{JPZX}	JTAG port high impedance to valid output	_	 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) 17 (for V_{CCIO} = 1.8 and 1.5 V) 	_	 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) 17 (for V_{CCIO} = 1.8 and 1.5 V) 	ns
t _{JPXZ}	JTAG port valid output to high impedance	_	 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) 17 (for V_{CCIO} = 1.8 and 1.5 V) 	_	 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) 17 (for V_{CCIO} = 1.8 and 1.5 V) 	ns



POR Specifications

Table 47: POR Delay Specifications for MAX 10 Devices—Preliminary

POR Delay	Condition	Minimum Maximum		Unit
Don't Care	Instant-on enabled	No delay		_
Fast	Instant-on disabled	3	9	ms
Standard	Instant-on disabled	50	200	ms

Remote System Upgrade Circuitry Timing Specifications

Table 48: Remote System Upgrade Circuitry Timing Specifications for MAX 10 Devices—Preliminary

Parameter	Device	Minimum	Maximum	Unit
t _{MAX_RU_CLK}	All	_	40	MHz
t	10M02, 10M04, 10M08, 10M16, 10M25	250	_	ns
^t RU_nCONFIG	10M40, 10M50	350	_	ns
t _{RU_nRSTIMER}	10M02, 10M04, 10M08, 10M16, 10M25	300	_	ns
	10M40, 10M50	500	_	ns

User Watchdog Internal Circuitry Timing Specifications

Table 49: User Watchdog Timer Specifications for MAX 10 Devices—Preliminary

The specifications are subject to PVT changes.

Parameter	Device	Minimum	Typical	Maximum	Unit
User watchdog frequency	10M02, 10M04, 10M08, 10M16, 10M25	3.4	5.1	7.3	MHz
	10M40, 10M50	2.2	3.3	4.8	MHz



Uncompressed Raw Binary File (.rbf) Sizes

Table 50: Uncompressed .rbf Sizes and Internal Configuration Time for MAX 10 Devices—Preliminary

The internal configuration time is based on the uncompressed, unencrypted, and without memory initialization files. Turn on instant-on feature to measure the internal configuration time. The internal configuration time measurement is from the minimum value of V_{CC_ONE} (for single supply devices) or V_{CC} (for dual supply devices) to user mode entry.

Device	CFM Data	Size (bits)	Internal Configuration Time (ms)	
Device	Without Memory Initialization	With Memory Initialization	internal Configuration Time (ins)	
10M02	554,000	676,000	3	
10M04	1,540,000	1,880,000	4	
10M08	1,540,000	1,880,000	4	
10M16	2,800,000	3,430,000	5	
10M25	4,140,000	4,780,000	5	
10M40	7,840,000	9,670,000	9	
10M50	7,840,000	9,670,000	9	

Related Information

Instant-on, MAX 10 FPGA Configuration User Guide

Provides more information about instant-on feature.

I/O Timing

The data is typically used prior to designing the FPGA to get an estimate of the timing budget as part of the link timing analysis.

The Quartus II Timing Analyzer provides a more accurate and precise I/O timing data based on the specific device and design after you complete place-and-route.



Table 51: I/O Timing for MAX 10 Devices—Preliminary

These I/O timing parameters are for the 3.3-V LVTTL I/O standard with the maximum drive strength and fast slew rate for 10M08DAF484 device.

Symbol	Parameter	-C7, −I7	-C8	Unit
T_{su}	Global clock setup time	-0.750	-0.808	ns
T_h	Global clock hold time	1.180	1.215	ns
T_{co}	Global clock to output delay	5.131	5.575	ns
T_{pd}	Best case pin-to-pin propagation delay through one LUT	4.907	5.467	ns

Programmable IOE Delay

Programmable IOE Delay On Row Pins

Table 52: IOE Programmable Delay on Row Pins for MAX 10 Devices—Preliminary

The incremental values for the settings are generally linear. For exact values of each setting, refer to the **Assignment Name** column in the latest version of the Quartus II software.

The minimum and maximum offset timing numbers are in reference to setting '0' as available in the Quartus II software.

		Number Mi		Maximum Offset						
Parameter	Paths Affected	Affected of		Fast Corner		Slow Corner				Unit
		Settings		- I 7	-C8	- C 7	-C8	- I 7	-A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	0.782	0.838	1.738	1.799	1.796	1.673	ns
Input delay from pin to input register	Pad to I/O input register	8	0	0.887	0.953	1.973	2.040	2.042	1.902	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.460	0.493	1.027	1.073	1.061	0.977	ns



Programmable IOE Delay for Column Pins

Table 53: IOE Programmable Delay on Column Pins for MAX 10 Devices—Preliminary

The incremental values for the settings are generally linear. For exact values of each setting, refer to the **Assignment Name** column in the latest version of the Quartus II software.

The minimum and maximum offset timing numbers are in reference to setting '0' as available in the Quartus II software.

	Number			Maximum Offset						
Parameter	Paths Affected	of	Minimum Offset	l Fast Corner L		Slow Corner				Unit
		Settings		- I 7	-C8	- C 7	-C8	- I 7	-A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	0.777	0.833	1.73	1.79	1.788	1.666	ns
Input delay from pin to input register	Pad to I/O input register	8	0	0.877	0.942	1.951	2.017	2.018	1.882	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.417	0.447	0.931	0.973	0.961	0.887	ns

Glossary

Table 54: Glossary

Term	Definition
Preliminary	Some tables show the designation as "Preliminary". Preliminary characteristics are created using simulation results, process data, and other known parameters.
	Final numbers are based on actual silicon characterization and testing. The numbers reflect the actual performance of the device under worst-case silicon process, voltage, and junction temperature conditions. There are no preliminary designations on finalized tables.
R_{L}	Receiver differential input discrete resistor (external to MAX 10 devices).



Term	Definition
RSKM (Receiver input skew margin)	HIGH-SPEED I/O block: The total margin left after accounting for the sampling window and TCCS. RSKM = (TUI – SW – TCCS) / 2.
Sampling window (SW)	HIGH-SPEED I/O Block: The period of time during which the data must be valid to capture it correctly. The setup and hold times determine the ideal strobe position in the sampling window.
Single-ended voltage referenced I/O standard	The AC input signal values indicate the voltage levels at which the receiver must meet its timing specifications. The DC input signal values indicate the voltage levels at which the final logic state of the receiver is unambiguously defined. After the receiver input crosses the AC value, the receiver changes to the new logic state.
	The new logic state is then maintained as long as the input stays beyond the DC threshold. This approach is intended to provide predictable receiver timing in the presence of input waveform ringing.
$t_{\rm C}$	High-speed receiver/transmitter input and output clock period.
TCCS (Channelto- channel-skew)	HIGH-SPEED I/O block: The timing difference between the fastest and slowest output edges, including $t_{\rm CO}$ variation and clock skew. The clock is included in the TCCS measurement.
t _{cin}	Delay from clock pad to I/O input register.
t _{CO}	Delay from clock pad to I/O output.
t _{cout}	Delay from clock pad to I/O output register.
t_{DUTY}	HIGH-SPEED I/O Block: Duty cycle on high-speed transmitter output clock.
t _{FALL}	Signal high-to-low transition time (80–20%).
t _H	Input register hold time.
Timing Unit Interval (TUI)	HIGH-SPEED I/O block: The timing budget allowed for skew, propagation delays, and data sampling window. (TUI = $1/(\text{Receiver Input Clock Frequency Multiplication Factor}) = t_C/w$).
t _{INJITTER}	Period jitter on PLL clock input.
t _{OUTJITTER_DEDCLK}	Period jitter on dedicated clock output driven by a PLL.
t _{OUTJITTER_IO}	Period jitter on general purpose I/O driven by a PLL.
t _{pllcin}	Delay from PLL inclk pad to I/O input register.
t _{pllcout}	Delay from PLL inclk pad to I/O output register.
t _{RISE}	Signal low-to-high transition time (20–80%).



Term	Definition
t_{SU}	Input register setup time.
V _{CM(DC)}	DC common mode input voltage.
V _{DIF(AC)}	AC differential input voltage: The minimum AC input differential voltage required for switching.
V _{DIF(DC)}	DC differential input voltage: The minimum DC input differential voltage required for switching.
V _{HYS}	Hysteresis for Schmitt trigger input.
V _{ICM}	Input common mode voltage: The common mode of the differential signal at the receiver.
V_{ID}	Input differential Voltage Swing: The difference in voltage between the positive and complementary conductors of a differential transmission at the receiver.
V_{IH}	Voltage input high: The minimum positive voltage applied to the input which is accepted by the device as a logic high.
V _{IH(AC)}	High-level AC input voltage.
V _{IH(DC)}	High-level DC input voltage.
V_{IL}	Voltage input low: The maximum positive voltage applied to the input which is accepted by the device as a logic low.
V _{IL (AC)}	Low-level AC input voltage.
V _{IL (DC)}	Low-level DC input voltage.
V _{IN}	DC input voltage.
V _{OCM}	Output common mode voltage: The common mode of the differential signal at the transmitter.
V_{OD}	Output differential voltage swing: The difference in voltage between the positive and complementary conductors of a differential transmission at the transmitter. $V_{OD} = V_{OH} - V_{OL}$.
V _{OH}	Voltage output high: The maximum positive voltage from an output which the device considers is accepted as the minimum positive high level.
V _{OL}	Voltage output low: The maximum positive voltage from an output which the device considers is accepted as the maximum positive low level.
V _{OS}	Output offset voltage: $V_{OS} = (V_{OH} + V_{OL}) / 2$.
V _{OX (AC)}	AC differential Output cross point voltage: The voltage at which the differential output signals must cross.



Term	Definition
$V_{ m REF}$	Reference voltage for SSTL, HSTL, and HSUL I/O Standards.
V _{REF(AC)}	AC input reference voltage for SSTL, HSTL, and HSUL I/O Standards. $V_{REF(AC)} = V_{REF(DC)} + noise$. The peak-to-peak AC noise on V_{REF} should not exceed 2% of $V_{REF(DC)}$.
V _{REF(DC)}	DC input reference voltage for SSTL, HSTL, and HSUL I/O Standards.
V _{SWING (AC)}	AC differential input voltage: AC Input differential voltage required for switching.
V _{SWING (DC)}	DC differential input voltage: DC Input differential voltage required for switching.
V_{TT}	Termination voltage for SSTL, HSTL, and HSUL I/O Standards.
V _{X (AC)}	AC differential Input cross point voltage: The voltage at which the differential input signals must cross.



Document Revision History for MAX 10 FPGA Device Datasheet

 Way 2015 Updated a note to V_{CCIO} for both single supply and dual supply power supplies recommended operating conditions tables. Note updated: V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities. Updated Example for OCT Resistance Calculation after Calibration at Device Power-Up. Removed a note to BLVDS in Differential I/O Standards Specifications for MAX 10 Devices table. BLVDS is now supported in MAX 10 single supply devices. Note removed: BLVDS TX is not supported in single supply devices. Updated ADC Performance Specifications for both single supply and dual supply devices. Changed the symbol for Operating junction temperature range parameter from T_A to T_J. Edited sampling rate maximum value from 1000 kSPS to 1 MSPS. Added a note to analog input voltage parameter. Removed input frequency, fi_{TN} specification. Updated the condition for DNL specification: External V_{REF}, no missing code. Added DNL specification for condition: Internal V_{REF}, no missing code. Added notes to AC accuracy specifications that the value with prescalar enabled is 6dB less than the specification. Added a note to On-Chip Temperature Sensor (absolute accuracy) parameter about the averaging calculation. Updated ADC Performance Specifications for MAX 10 Single Supply Devices table. Added condition for On-Chip Temperature Sensor (absolute accuracy) parameter: with 64 samples averaging. Updated ADC Performance Specifications for MAX 10 Dual Supply Devices table. Updated Digital Supply Voltage minimum value from 1.14 V to 1.15 V and maximum value from 1.26 V to 1.25 V. 	Date	Version	Changes
	May 2015	2015.05.04	conditions tables. Note updated: V _{CCIO} for all I/O banks must be powered up during user mode because V _{CCIO} I/O banks are used for the ADC and I/O functionalities. • Updated Example for OCT Resistance Calculation after Calibration at Device Power-Up. • Removed a note to BLVDS in Differential I/O Standards Specifications for MAX 10 Devices table. BLVDS is now supported in MAX 10 single supply devices. Note removed: BLVDS TX is not supported in single supply devices. • Updated ADC Performance Specifications for both single supply and dual supply devices. • Changed the symbol for Operating junction temperature range parameter from T _A to T _J . • Edited sampling rate maximum value from 1000 kSPS to 1 MSPS. • Added a note to analog input voltage parameter. • Removed input frequency, f _{IN} specification: • Updated the condition for DNL specification: External V _{REF} , no missing code. Added DNL specification for condition: Internal V _{REF} , no missing code. • Added notes to AC accuracy specifications that the value with prescalar enabled is 6dB less than the specification. • Added a note to On-Chip Temperature Sensor (absolute accuracy) parameter about the averaging calculation. • Updated ADC Performance Specifications for MAX 10 Single Supply Devices table. • Added condition for On-Chip Temperature Sensor (absolute accuracy) parameter: with 64 samples averaging. • Updated ADC Performance Specifications for MAX 10 Dual Supply Devices table. • Updated ADC Performance Specifications for MAX 10 Dual Supply Devices table.



Date	Version	Changes
		• Updated f _{HSCLK} and HSIODR specifications for –A7 speed grade in the following tables:
		 True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True LVDS Transmitter Timing Specifications for MAX 10 Single Supply Devices True LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices Emulated LVDS_E_3R Transmitter Timing Specifications for MAX 10 Single Supply Devices Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices LVDS Receiver Timing Specifications for MAX 10 Single Supply Devices LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for MAX 10 Dual Supply
		Devices • Updated TCCS specifications in the following tables:
		 True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices Emulated RSDS_E_1R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True LVDS Transmitter Timing Specifications for MAX 10 Single Supply Devices True LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices
		 Emulated LVDS_E_3R Transmitter Timing Specifications for MAX 10 Single Supply Devices Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices



Date	Version	Changes
		Updated t _{x Jitter} specifications in the following tables:
		 True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices Emulated RSDS_E_1R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for MAX 10 Dual Supply Devices True LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices Updated SW specifications in LVDS Receiver Timing Specifications for MAX 10 Single Supply Devices table. Added a note to t_{x Jitter} for all LVDS tables. Note: TX jitter is the jitter induced from core noise and I/O switching noise. Updated the description for t_{LOCK} for all LVDS tables: Time required for the PLL to lock, after CONF_DONE
		signal goes high, indicating the completion of device configuration. • Updated Memory Output Clock Jitter Specifications section.
		 Updated maximum external memory interfaces frequency from 300 MHz to 303 MHz. Updated PLL output routing from global clock network to PHY clock network. Added I/O Timing for MAX 10 Devices table. Added V_{HYS} in the Glossary table.
January 2015	2015.01.23	 Removed a note to V_{CCA} in Power Supplies Recommended Operating Conditions for MAX 10 Dual Supply Devices table. This note is not valid: All V_{CCA} pins must be connected together for EQFP package. Corrected the maximum value for t_{OUTJITTER_CCJ_IO} (F_{OUT} ≥ 100 MHz) from 60 ps to 650 ps in PLL Specifications for MAX 10 Devices table.



Date	Version	Changes
December 2014	2014.12.15	 Restructured Programming/Erasure Specifications for MAX 10 Devices table to add temperature specifications that affect the data retention duration. Added statements in the I/O Pin Leakage Current section: Input channel leakage of ADC I/O pins due to hot socket is up to maximum of 1.8 mA. The input channel leakage occurs when the ADC IP core is enabled or disabled. This is applicable to all MAX 10 devices with ADC IP core, which are 10M04, 10M08, 10M16, 10M25, 10M40, and 10M50 devices. The ADC I/O pins are in Bank 1A. Added a statement in the I/O Standards Specifications section: You must perform timing closure analysis to determine the maximum achievable frequency for general purpose I/O standards. Updated SSTL-2 Class I and II I/O standard specifications for JEDEC compliance as follows: VIL(AC) Max: Updated from V_{REF} – 0.35 to V_{REF} – 0.31
		 VIH(AC) Min: Updated from V_{REF} + 0.35 to V_{REF} + 0.31 Added a note to BLVDS in Differential I/O Standards Specifications for MAX 10 Devices table: BLVDS TX is not supported in single supply devices. Added a link to MAX 10 High-Speed LVDS I/O User Guide for the list of I/O standards supported in single supply and dual supply devices. Added a statement in PLL Specifications for MAX 10 Single Supply Device table: For V36 package, the PLL specification is based on single supply devices. Added Internal Oscillator Specifications from MAX 10 Clocking and PLL User Guide. Added UFM specifications for serial interface. Updated total harmonic distortion (THD) specifications as follows:
		 Single supply devices: Updated from 65 dB to -65 dB Dual supply devices: Updated from 70 dB to -70 dB (updated from 65 dB to -65 dB for dual function pin) Added condition for On-Chip Temperature Sensor—Absolute accuracy parameter in ADC Performance Specifications for MAX 10 Dual Supply Devices table. The condition is: with 64 samples averaging. Updated the description in Periphery Performance Specifications to mention that proper timing closure is required in design. Updated HSIODR and f_{HSCLK} specifications for x10 and x7 modes in True LVDS Transmitter Timing Specifications for MAX 10 Dual Supply Devices.



Date	Version	Changes
		 Added specifications for low-speed I/O performance pin sampling window in LVDS Receiver Timing Specifications for MAX 10 Single Supply Devices table: Max = 900 ps for -C7, -I7, -A7, and -C8 speed grades. Added t_{RU_nCONFIG} and t_{RU_nRSTIMER} specifications for different devices in Remote System Upgrade Circuitry Timing Specifications for MAX 10 Devices table. Removed the word "internal oscillator" in User Watchdog Timer Specifications for MAX 10 Devices table to avoid confusion. Added IOE programmable delay specifications.
September 2014	2014.09.22	Initial release.

